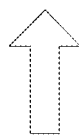
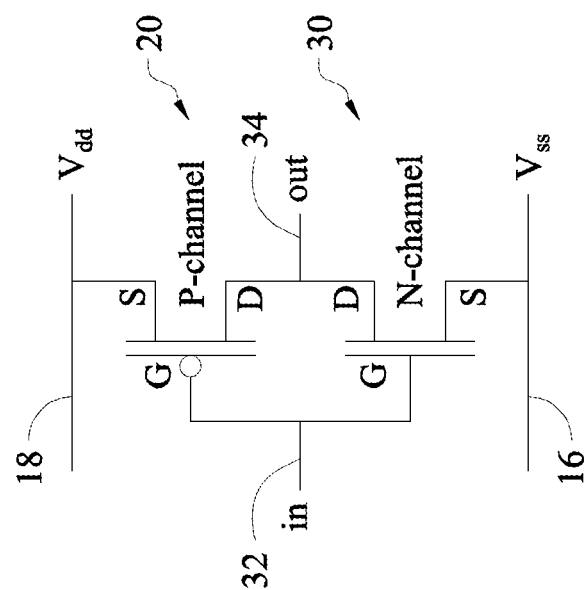
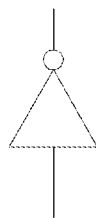


Figure 1

Circuit diagram (inverter)



Top down

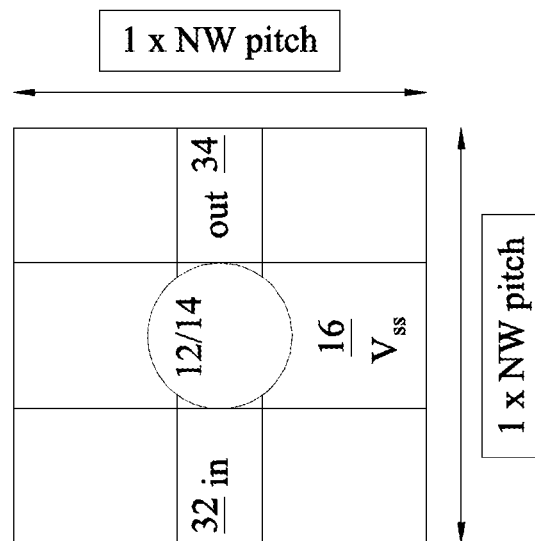


Figure 2

Figure 3

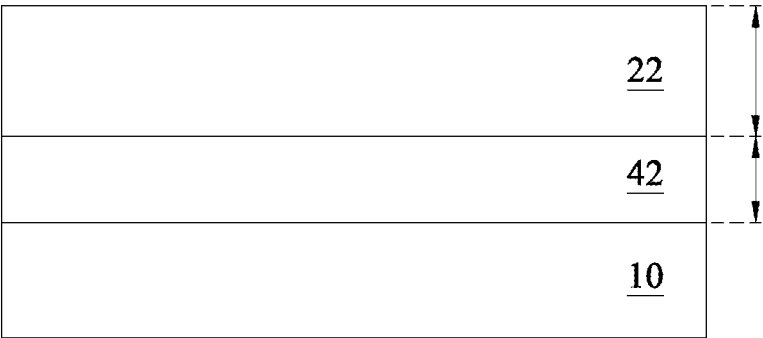


Figure 4A

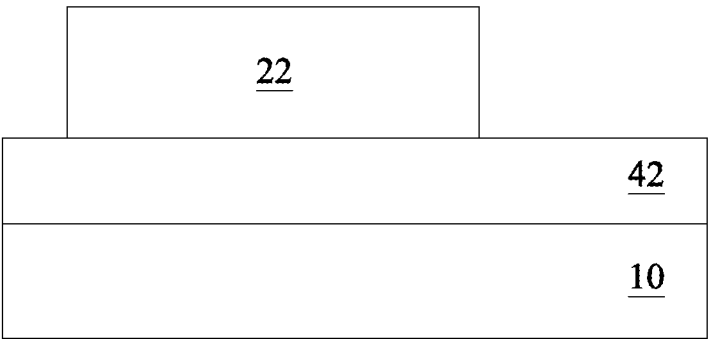


Figure 4B

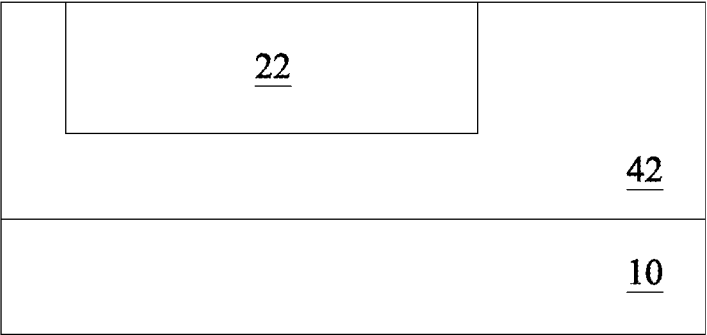


Figure 4C

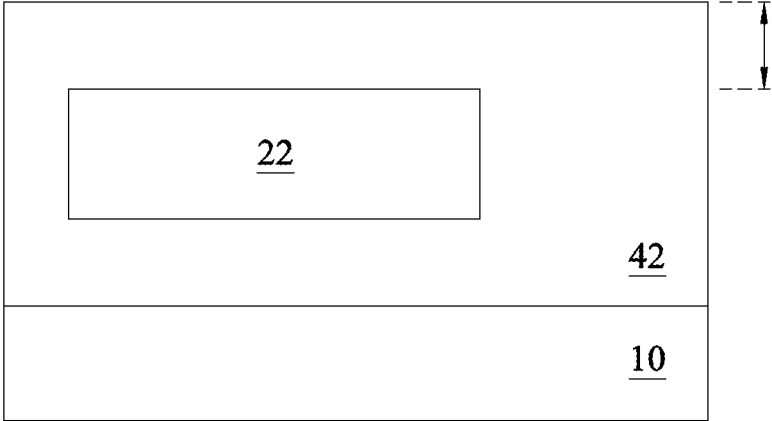


Figure 4D

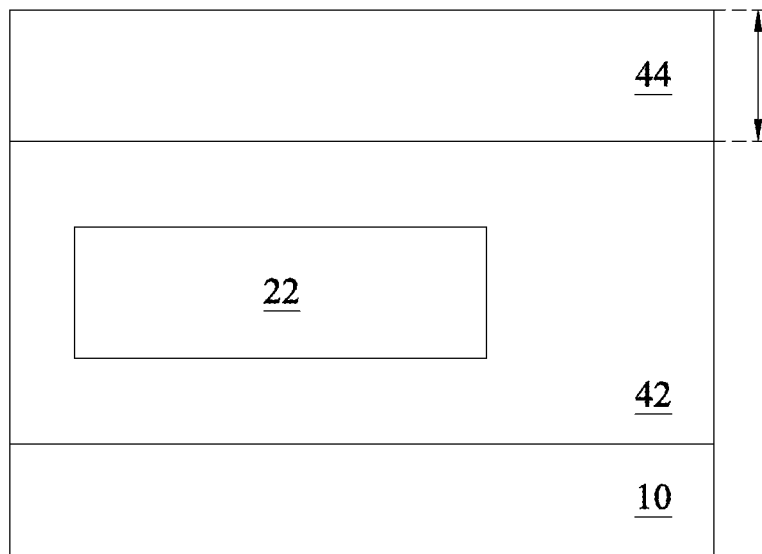


Figure 4E

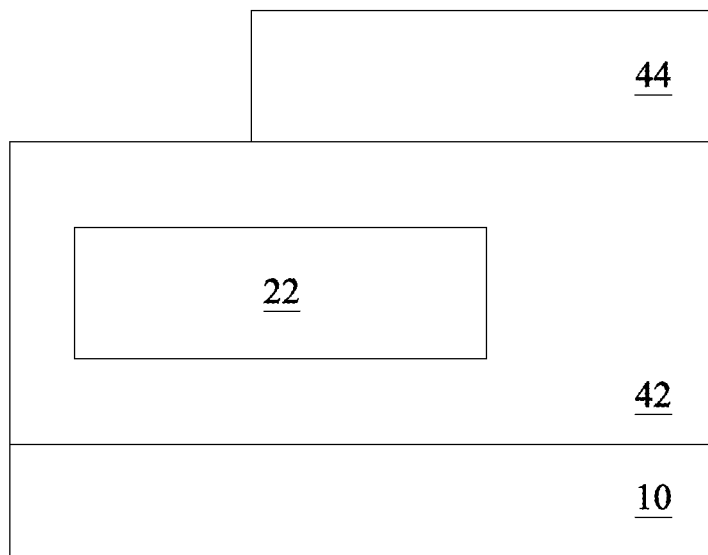


Figure 4F

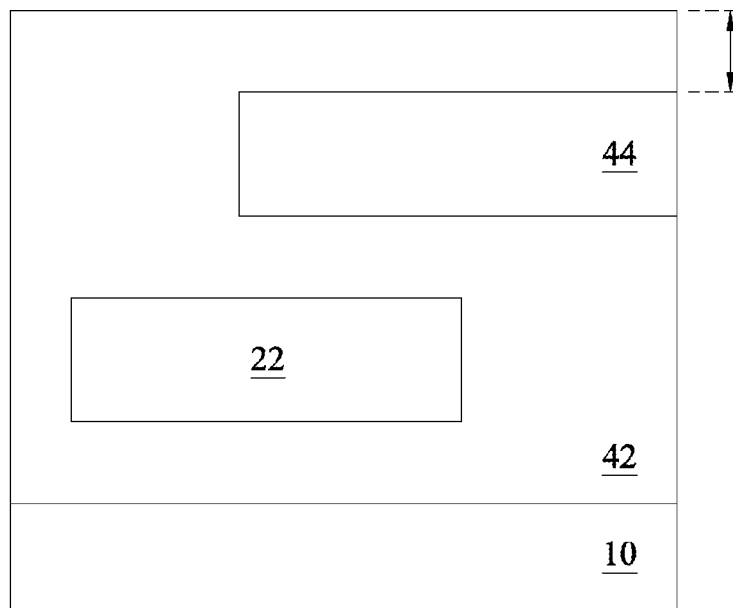


Figure 4G

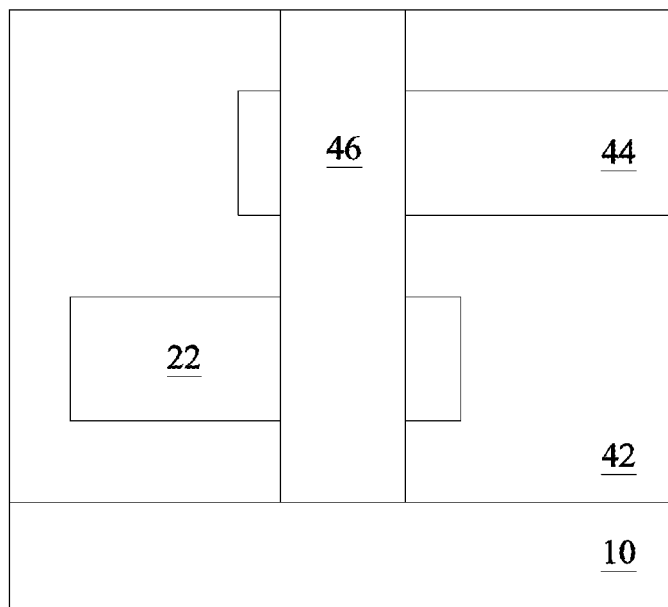


Figure 4H

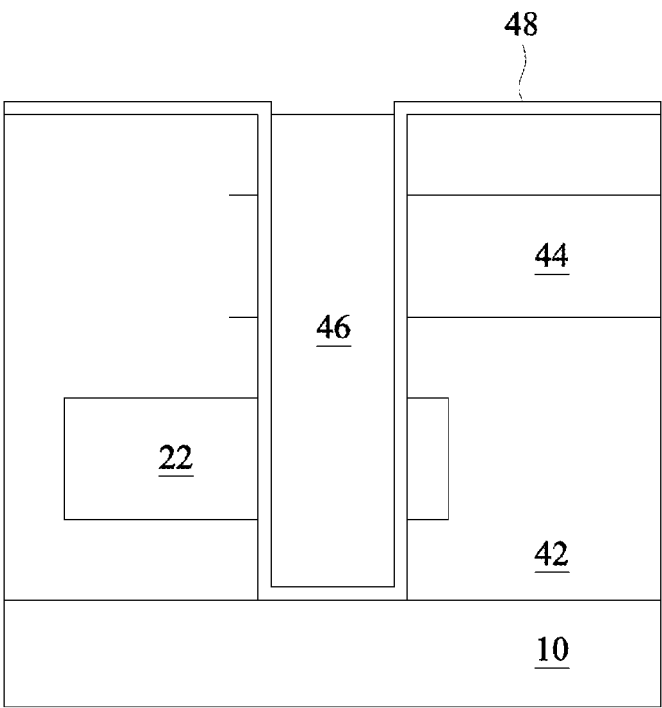


Figure 4I

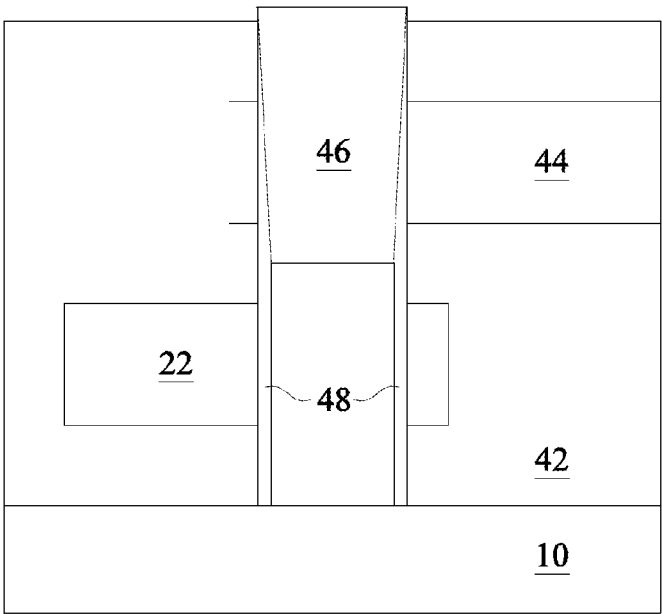


Figure 4J

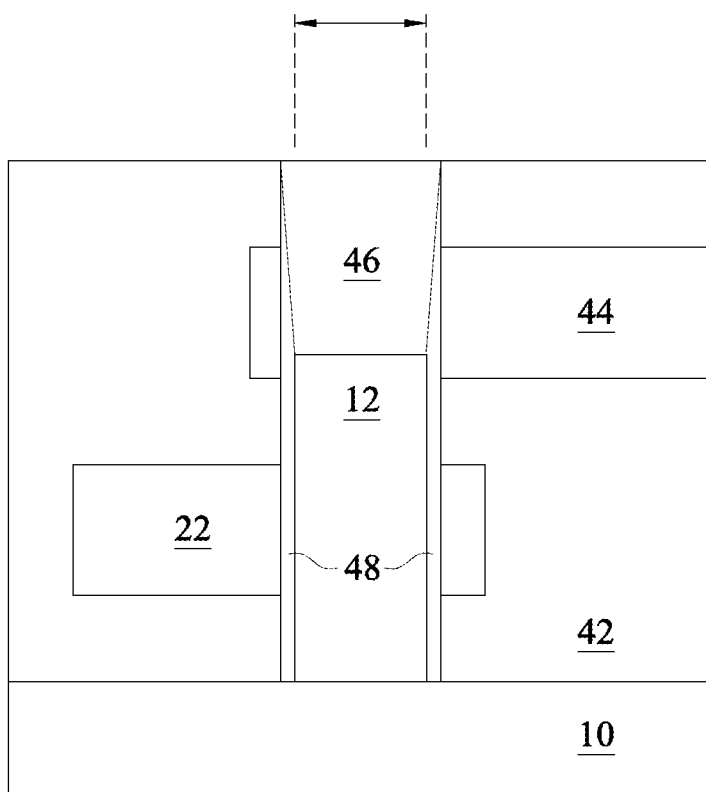


Figure 4K

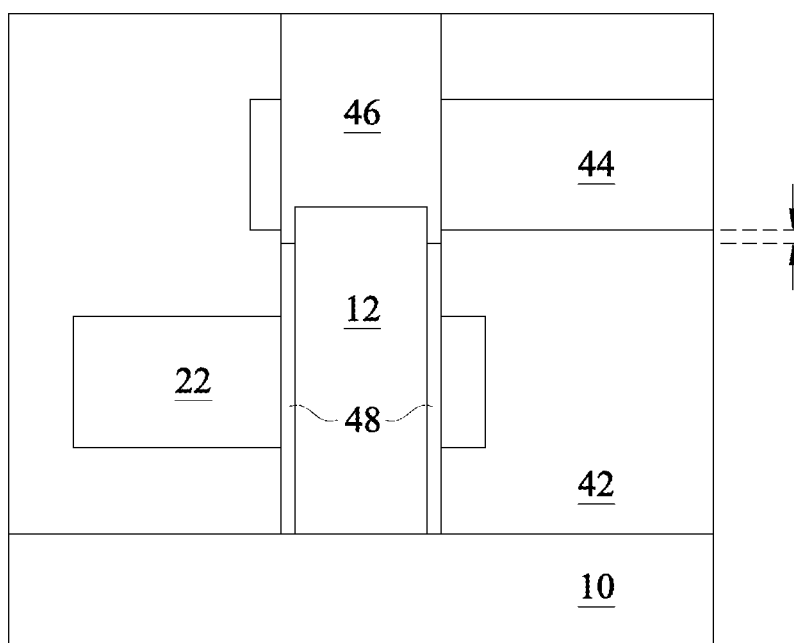


Figure 4L

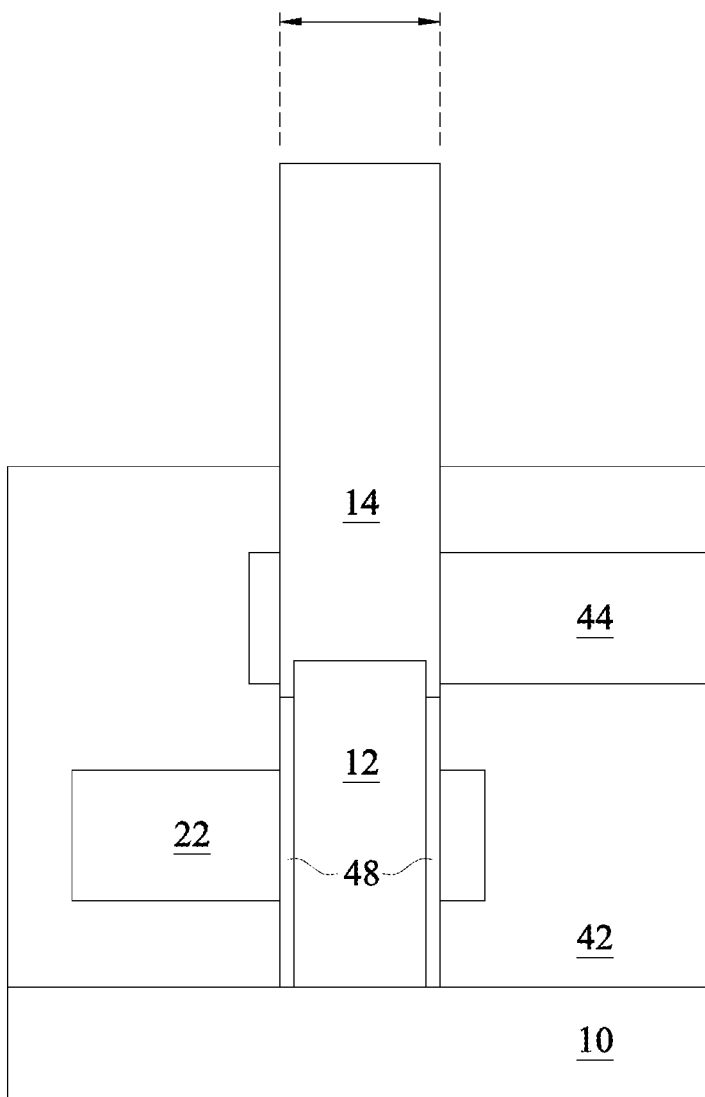


Figure 4M

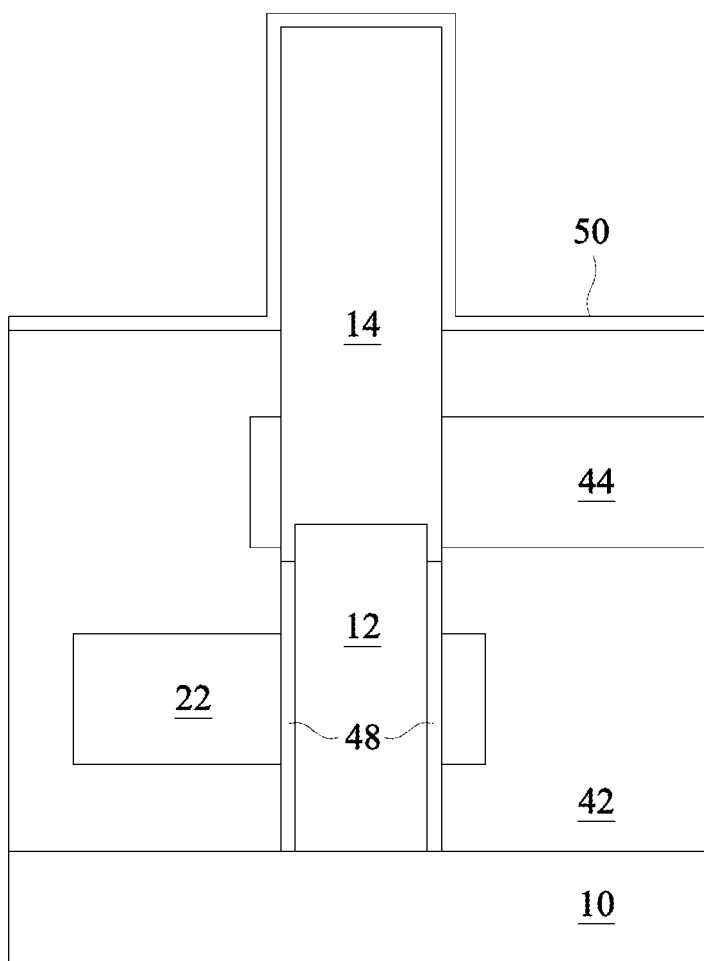


Figure 4N

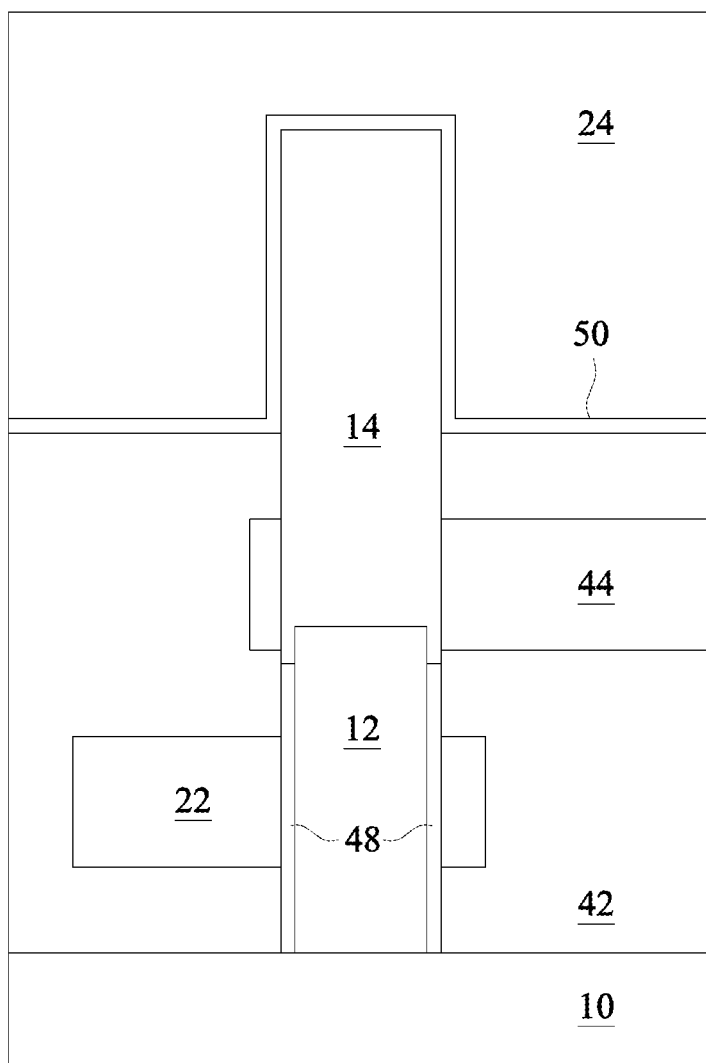


Figure 40

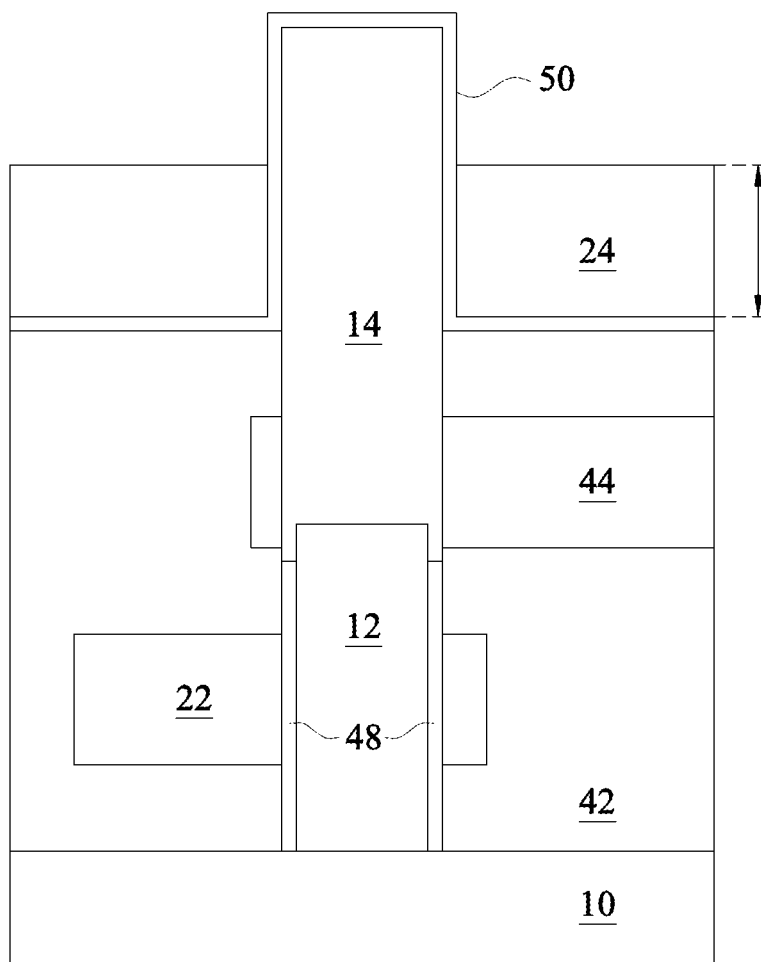


Figure 4P

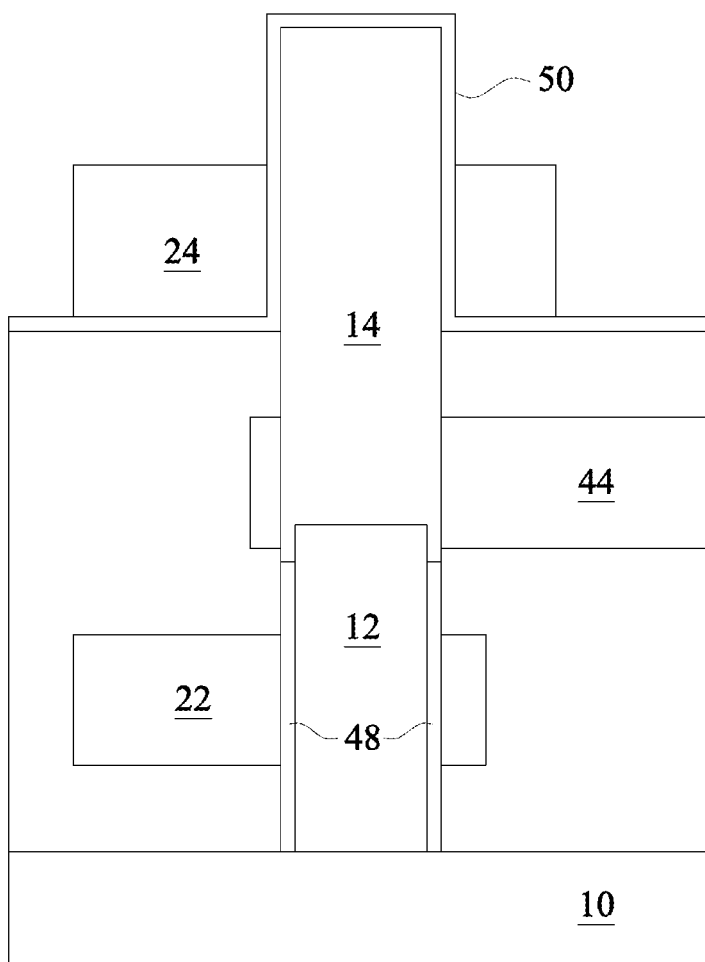


Figure 4Q

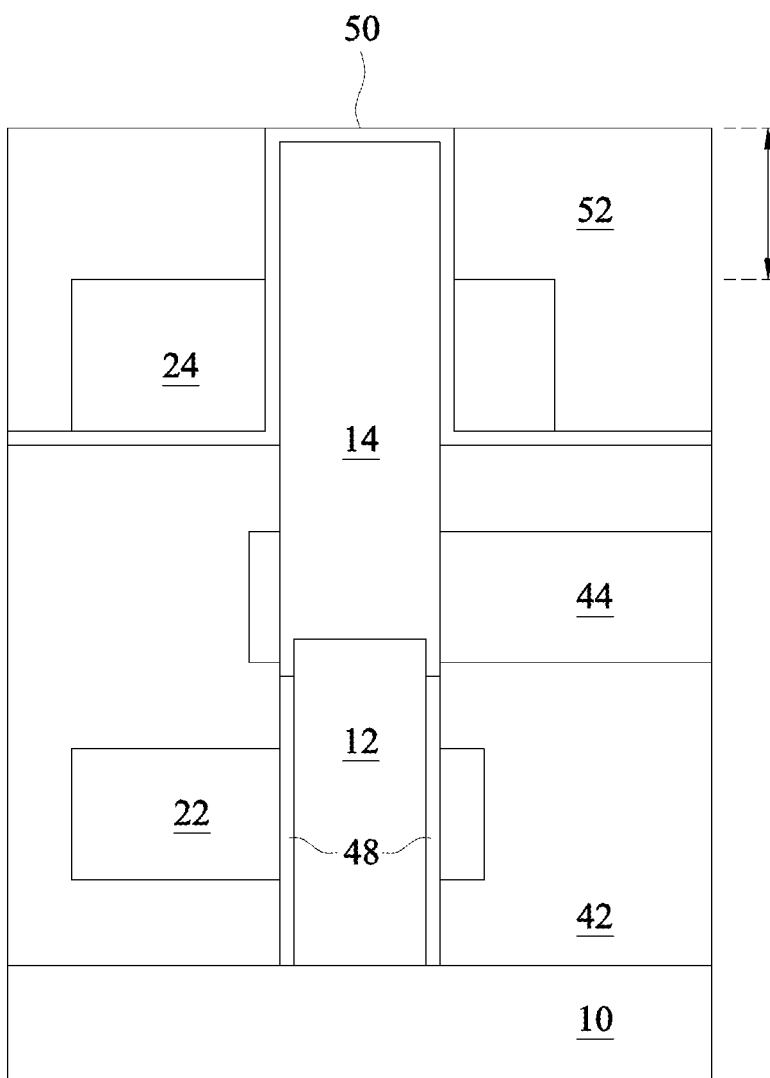


Figure 4R

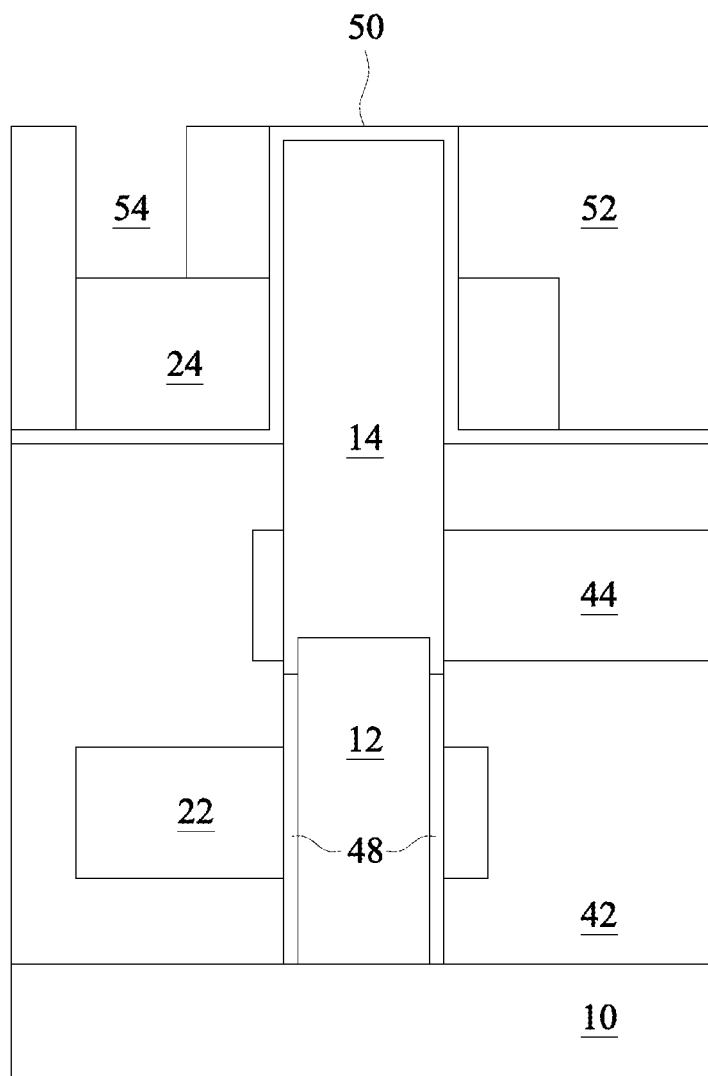


Figure 4S

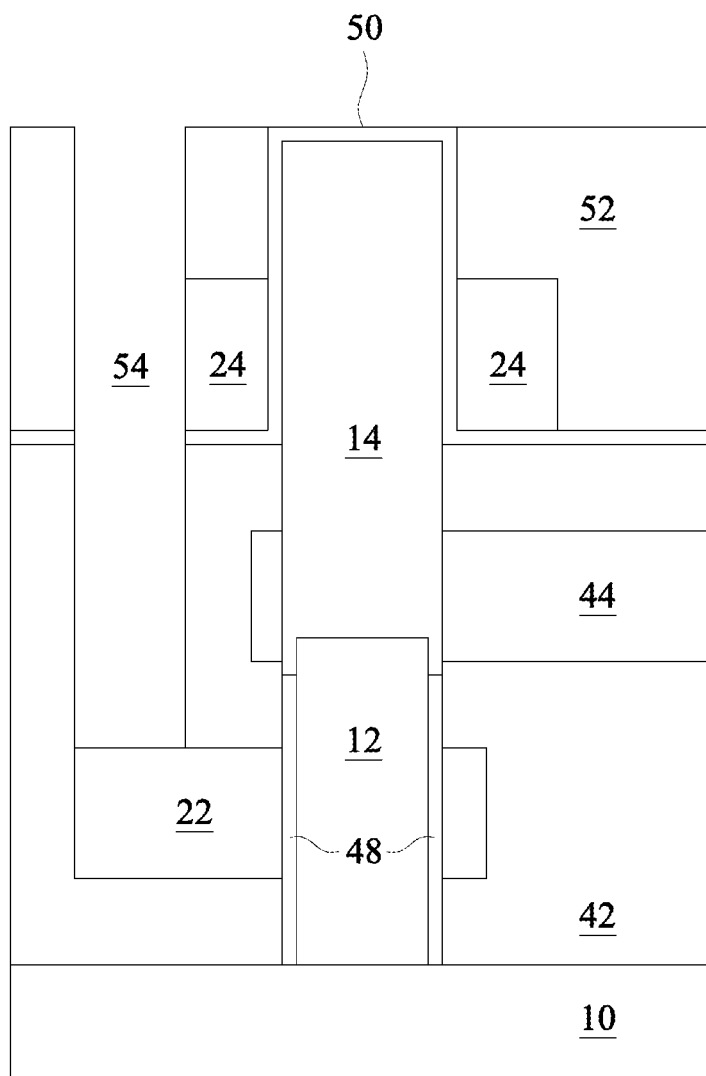


Figure 4T

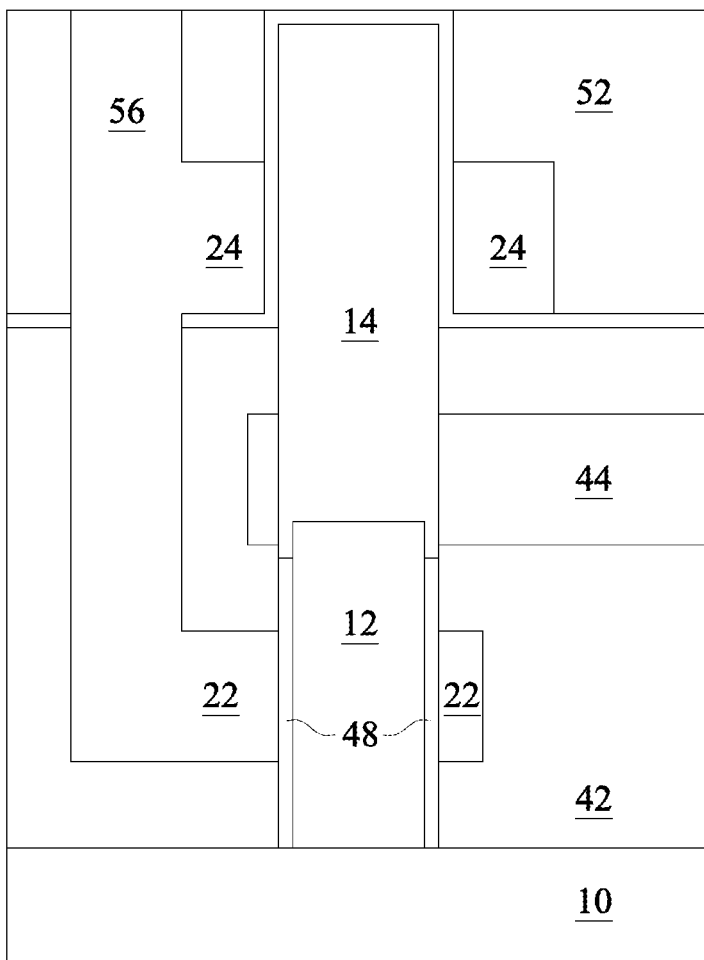


Figure 4U

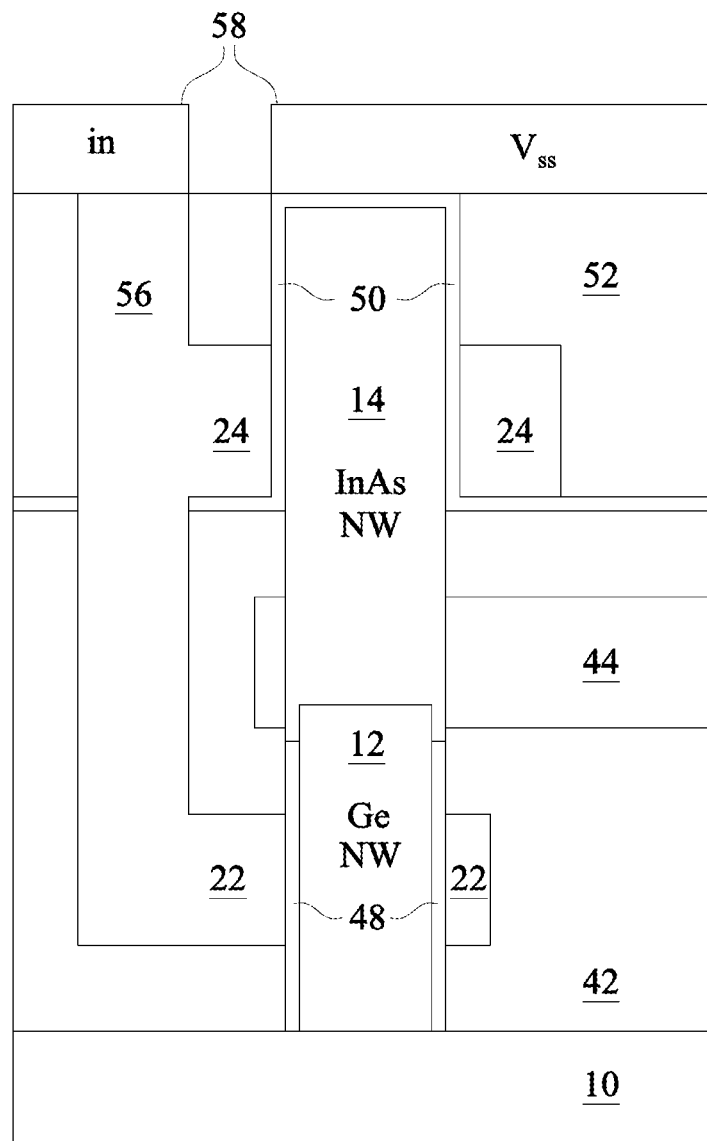


Figure 4V

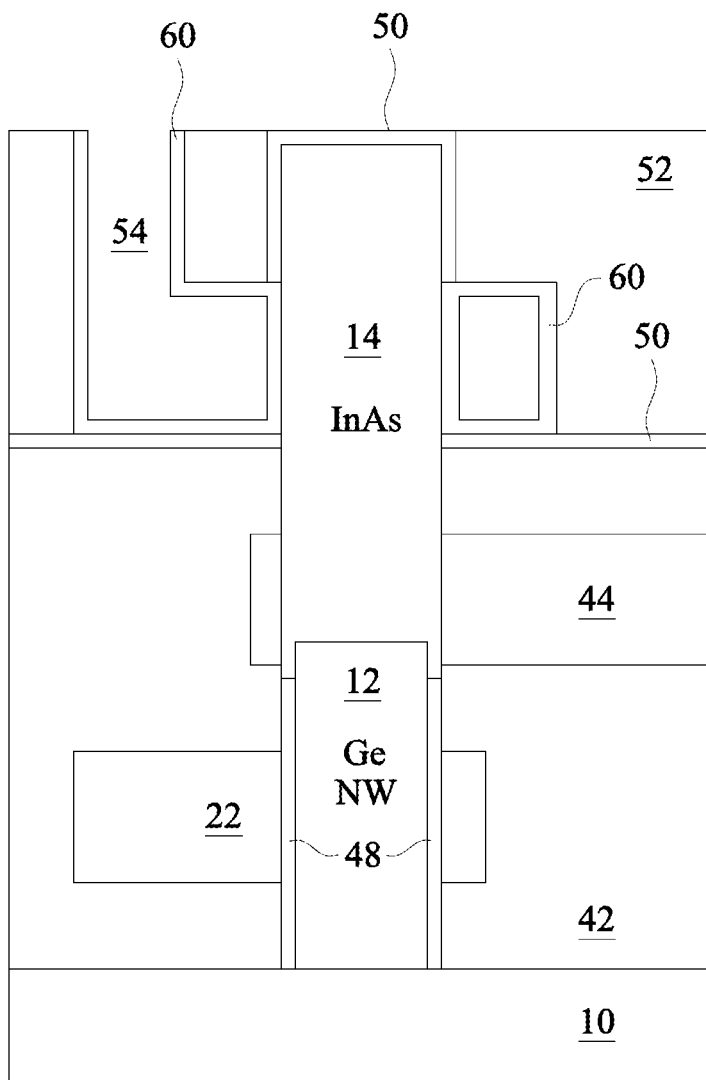


Figure 5A

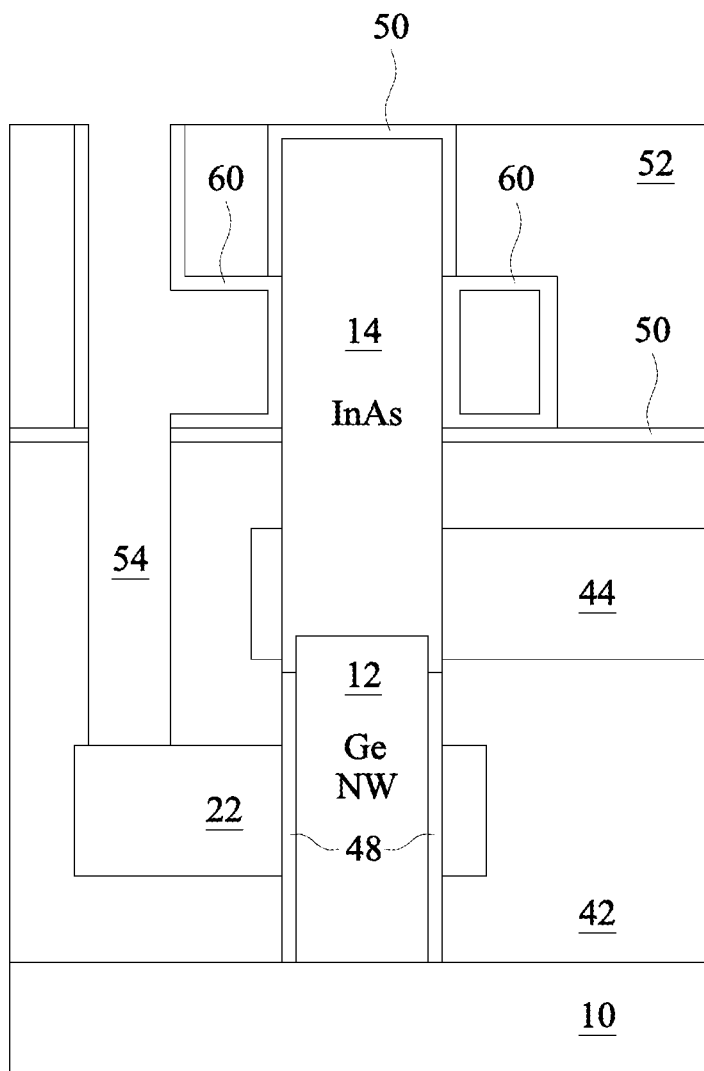


Figure 5B

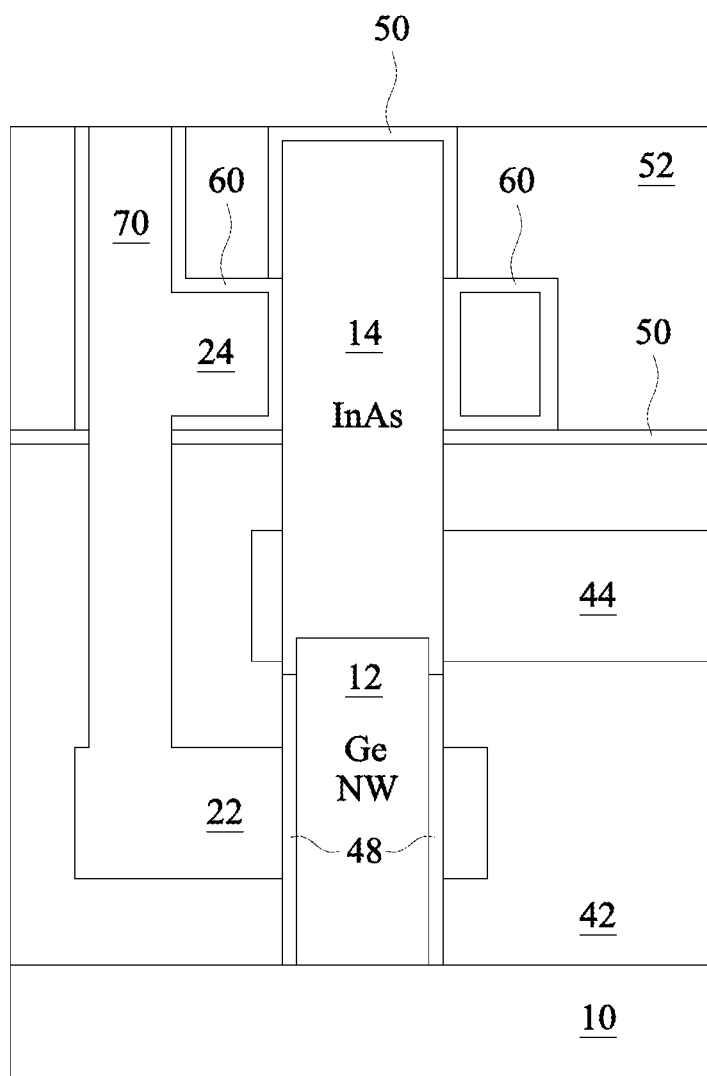


Figure 5C

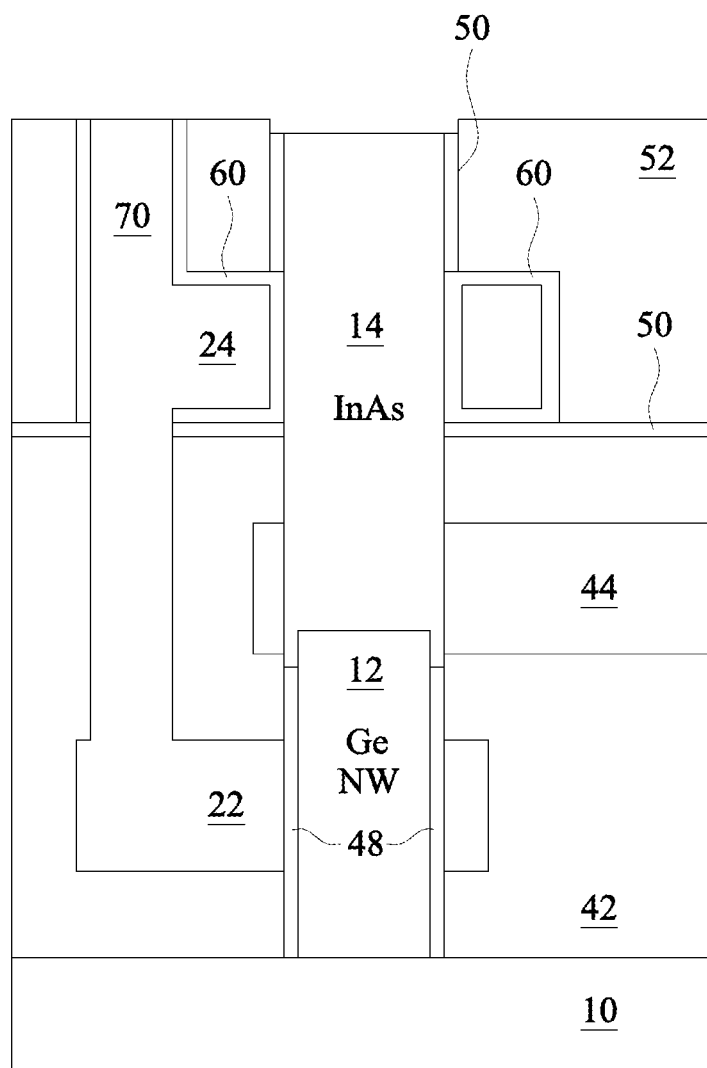


Figure 5D

Figure 5E

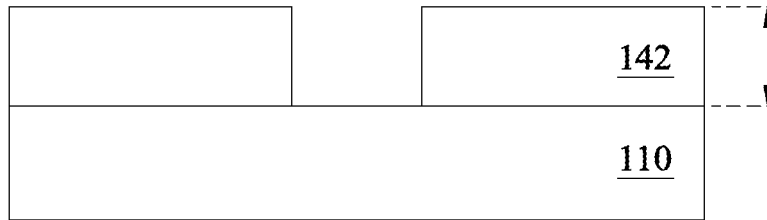


Figure 6A

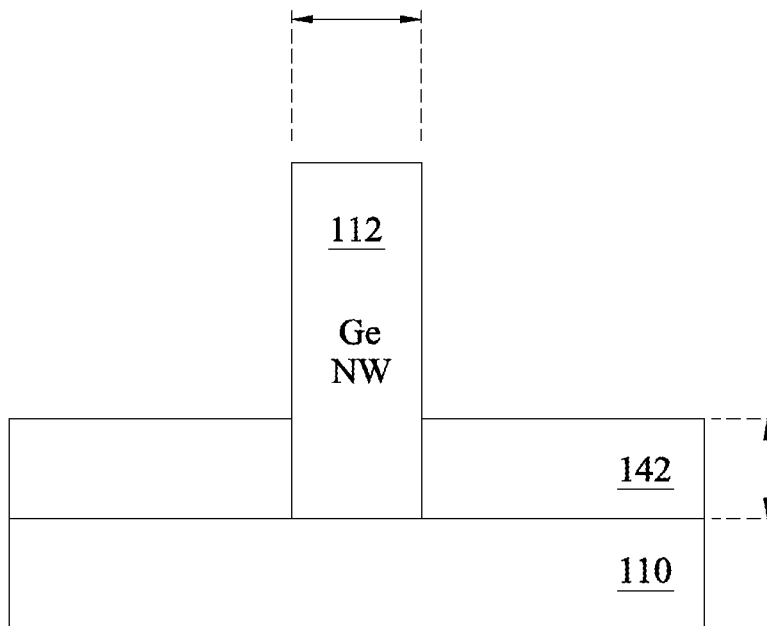


Figure 6B

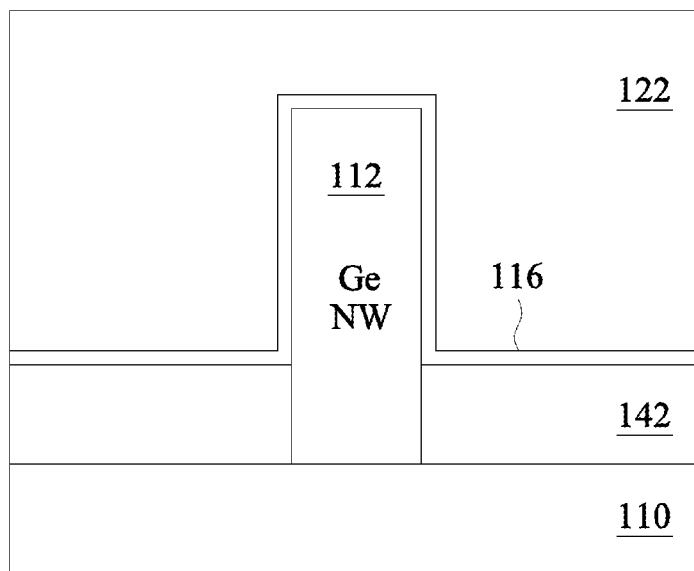


Figure 6C

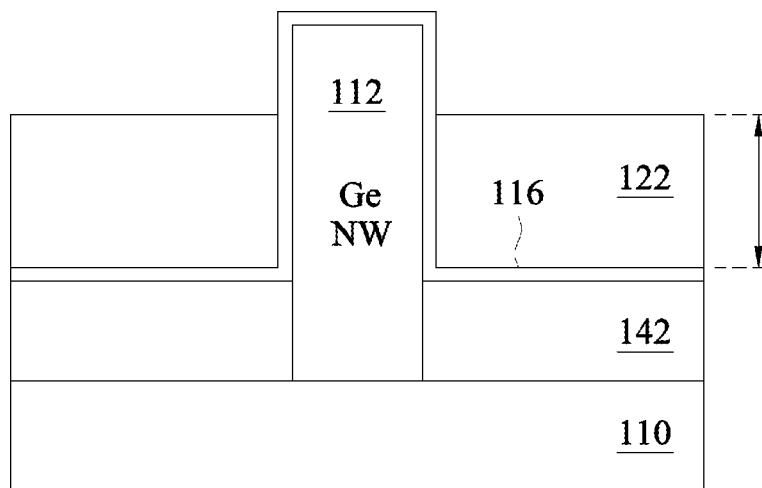


Figure 6D

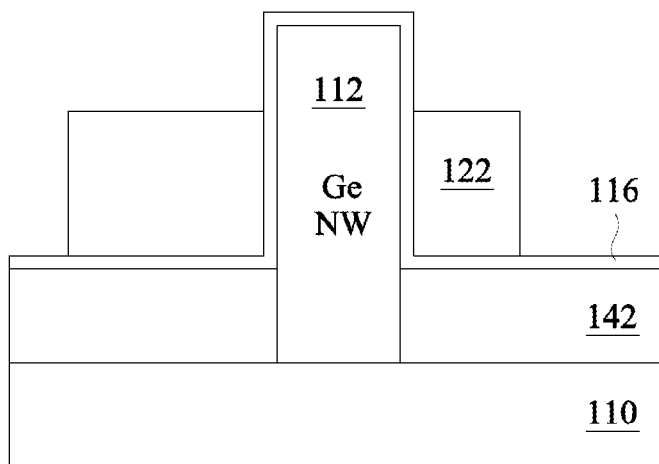


Figure 6E

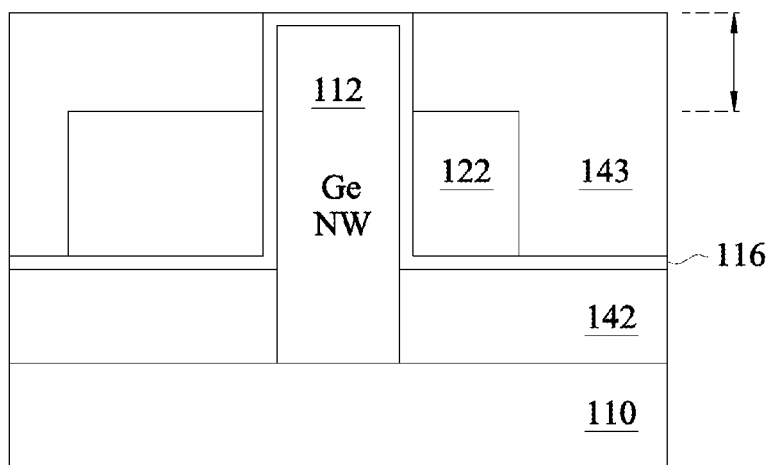


Figure 6F

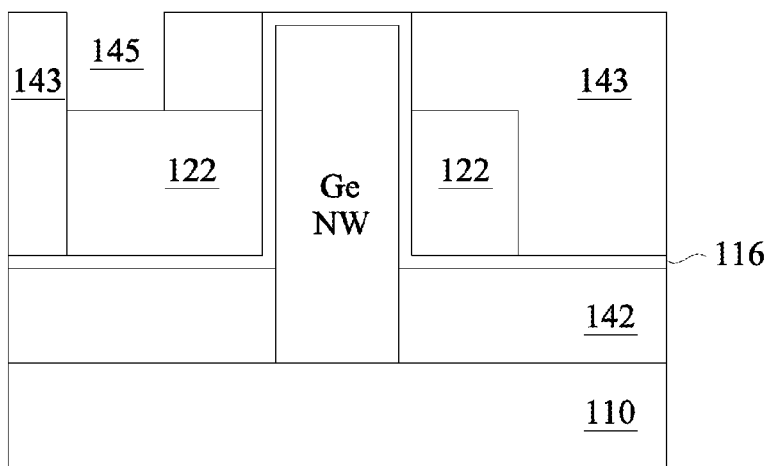


Figure 6G

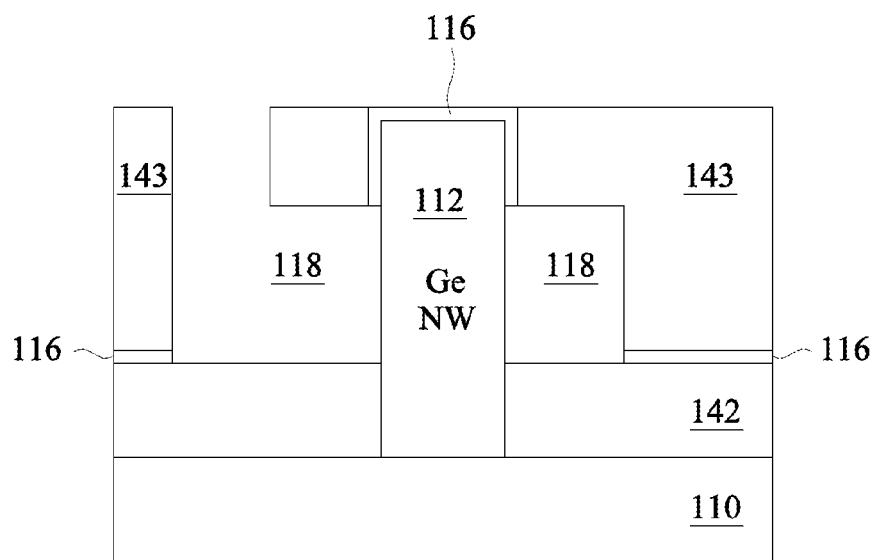


Figure 6H

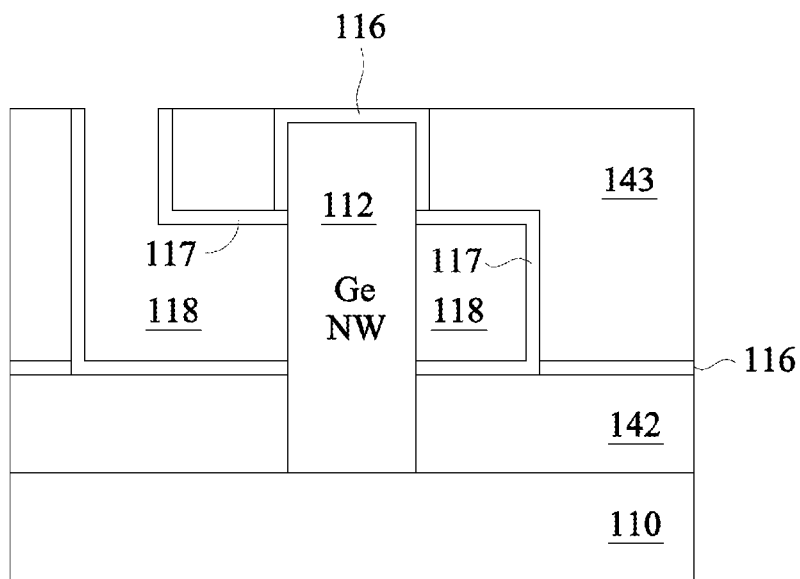


Figure 6I

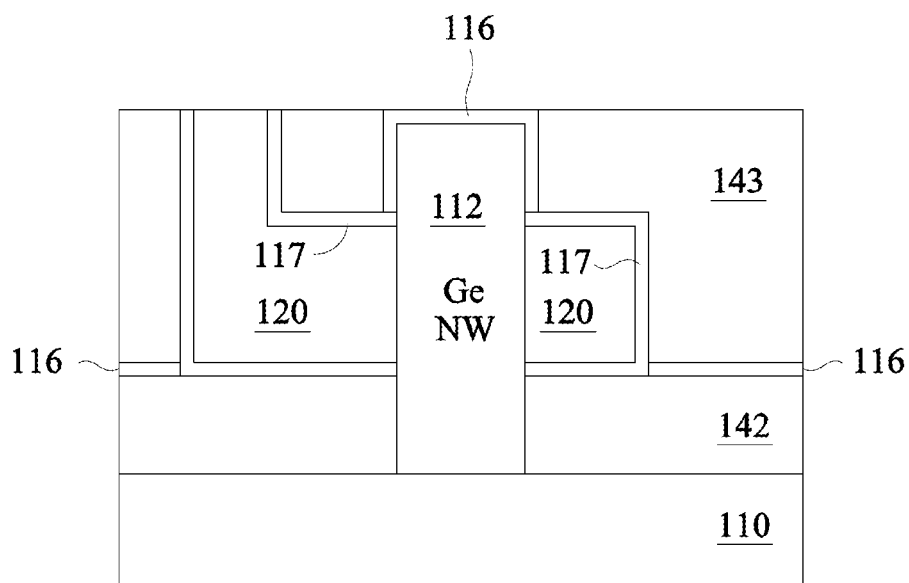


Figure 6J

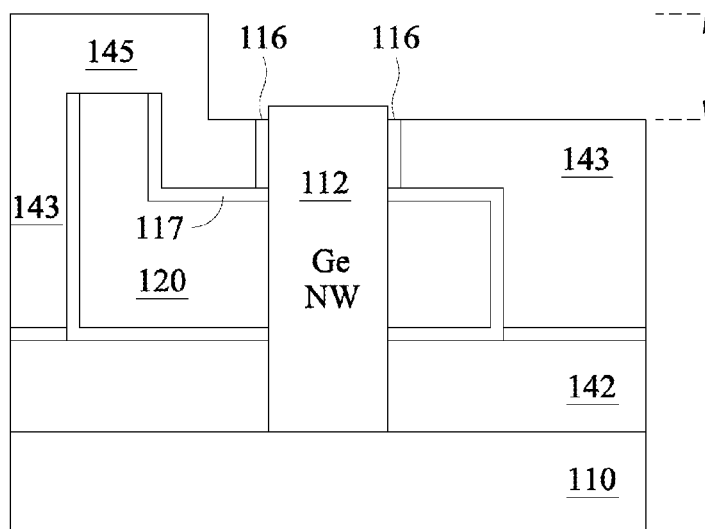


Figure 6K

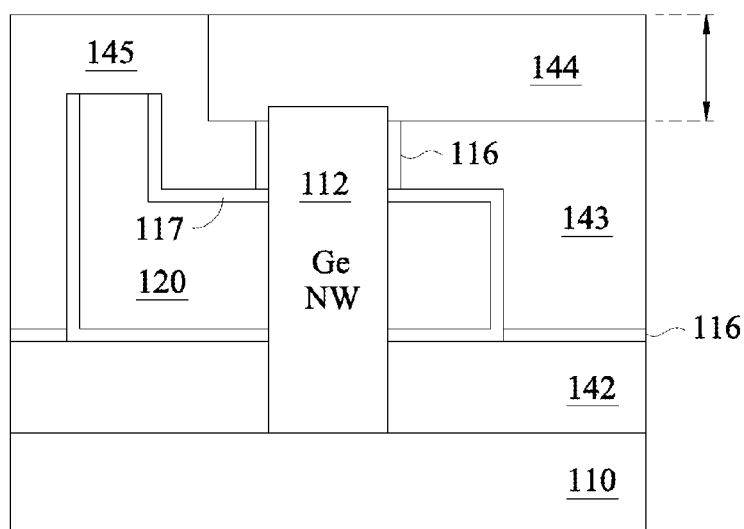


Figure 6L

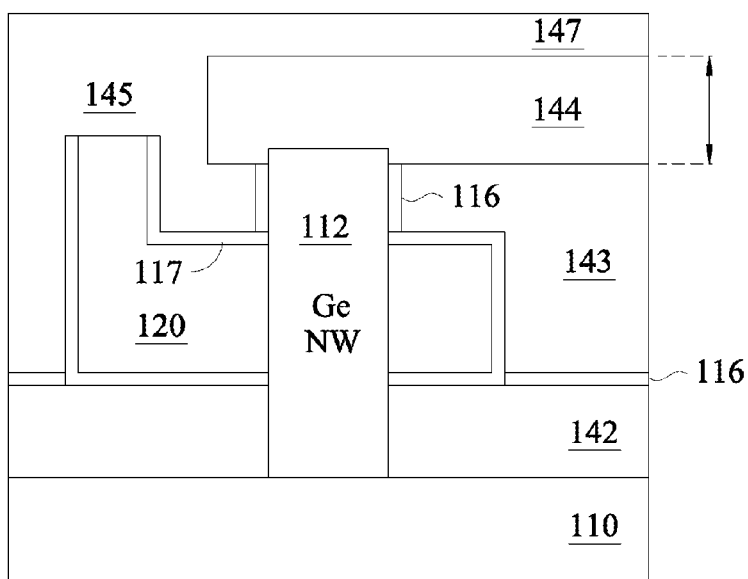


Figure 6M

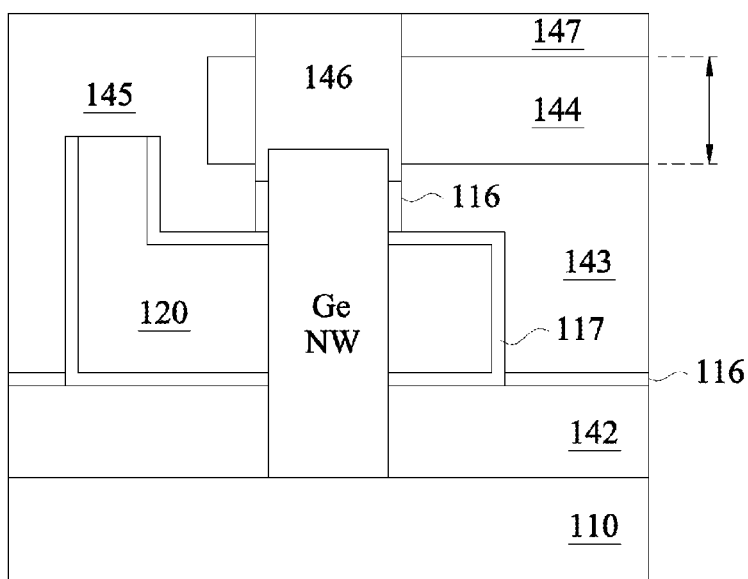


Figure 6N

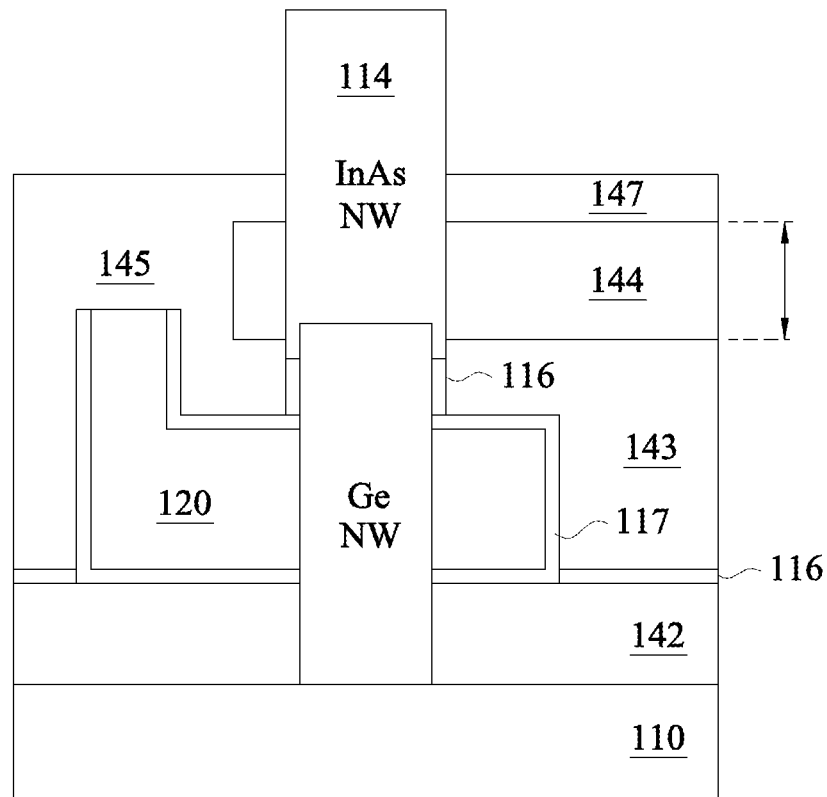


Figure 6O

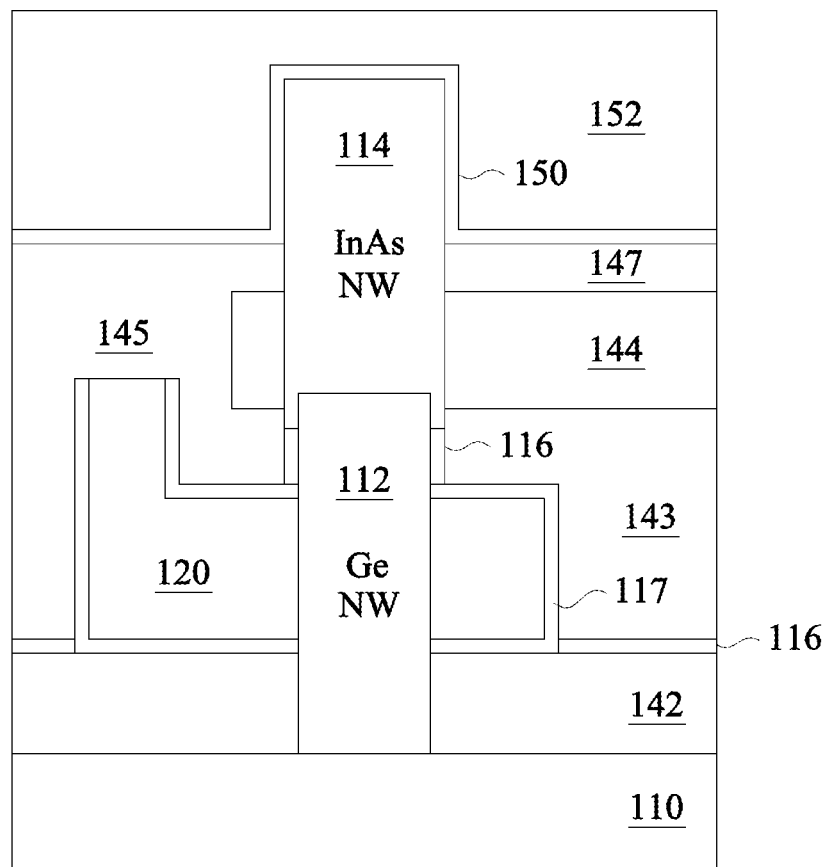


Figure 6P

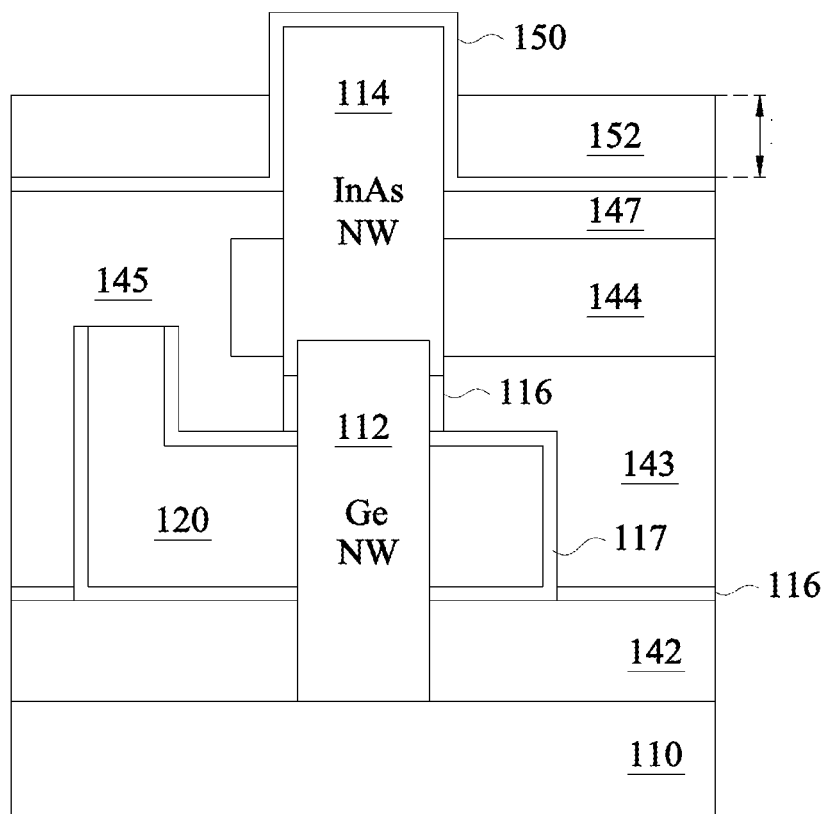


Figure 6Q

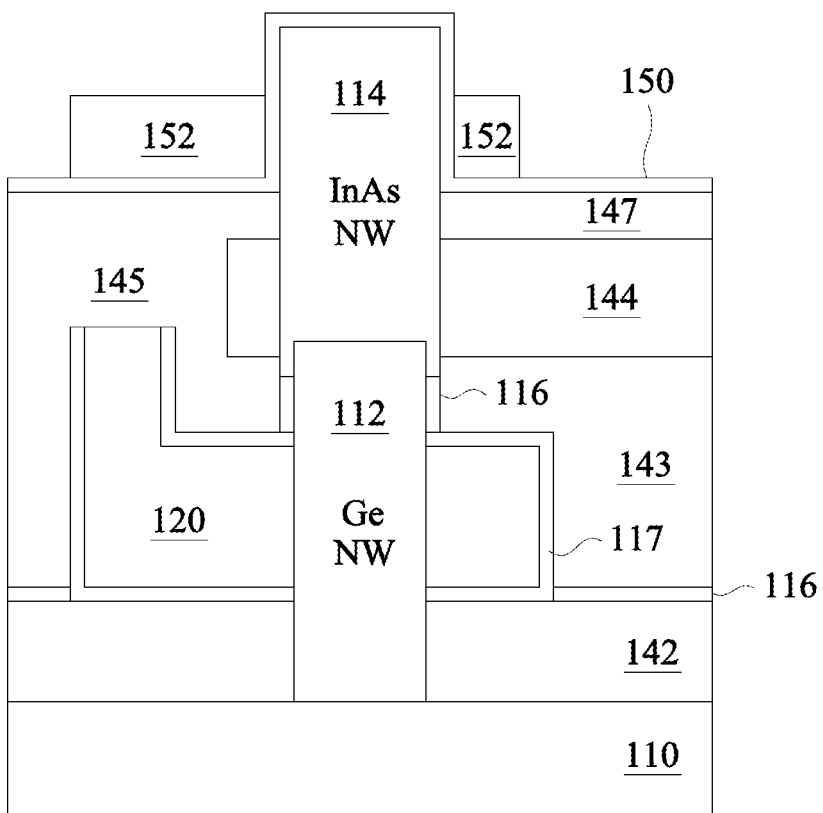


Figure 6R

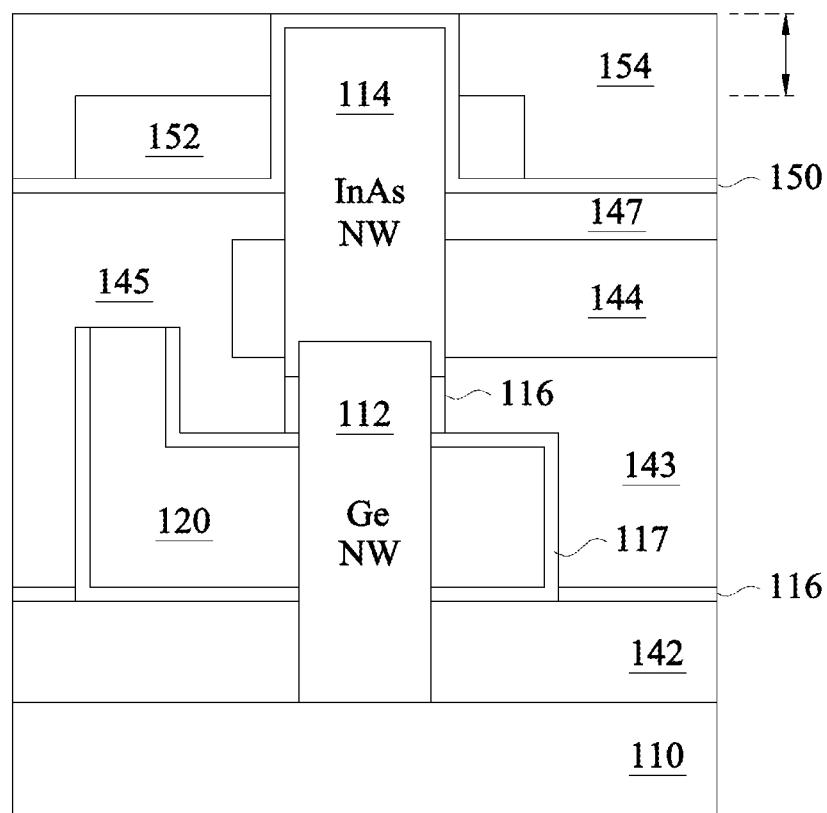


Figure 6S

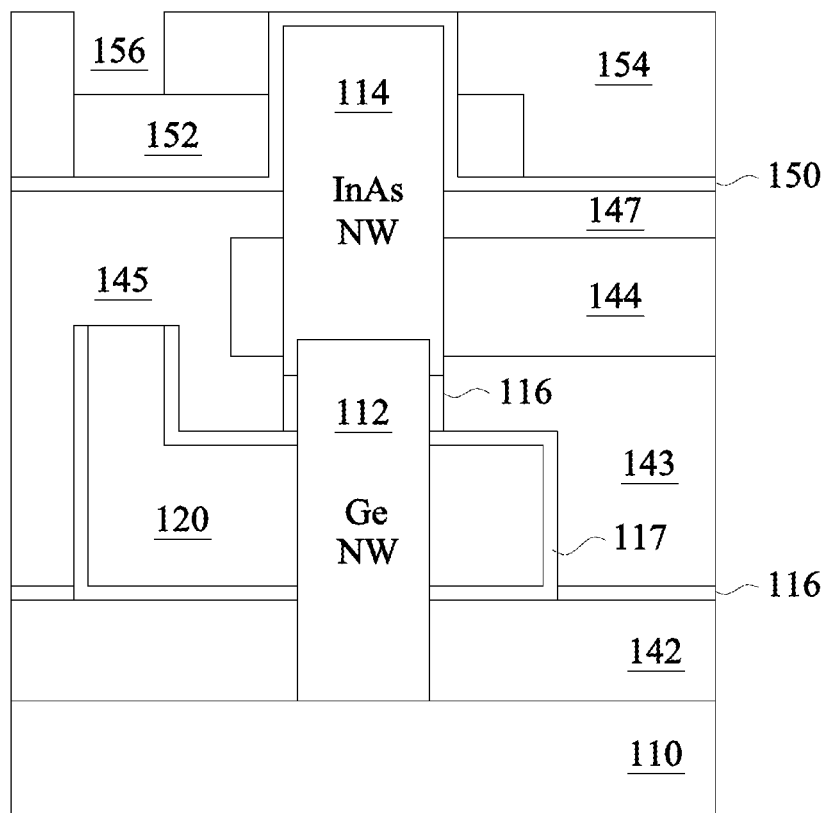


Figure 6T

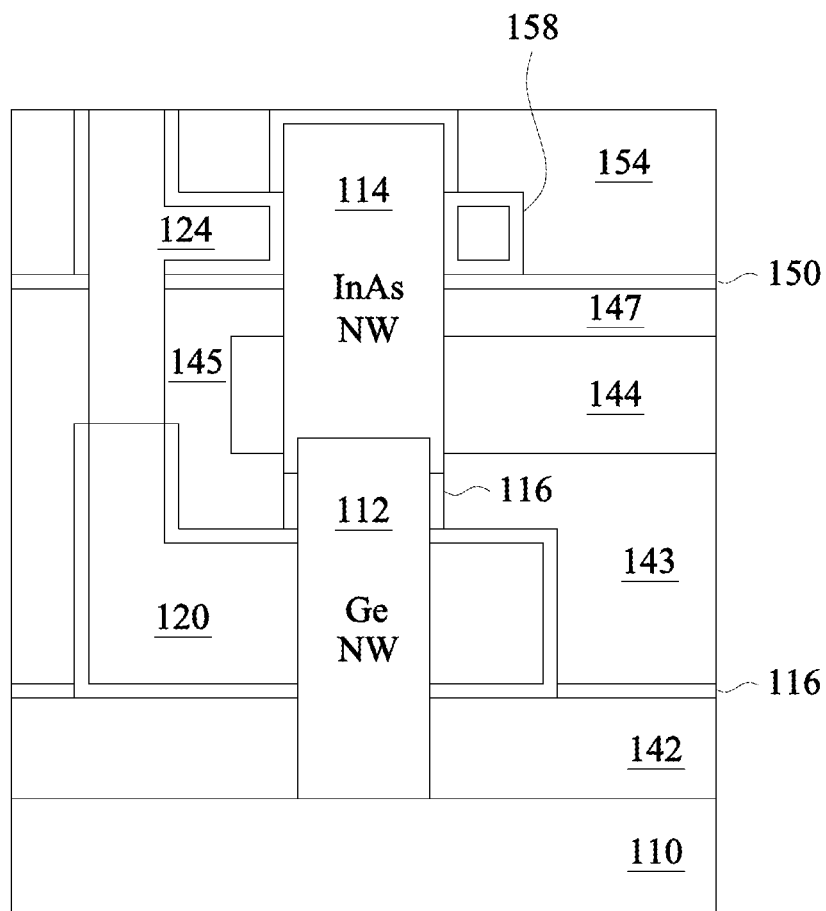


Figure 6V

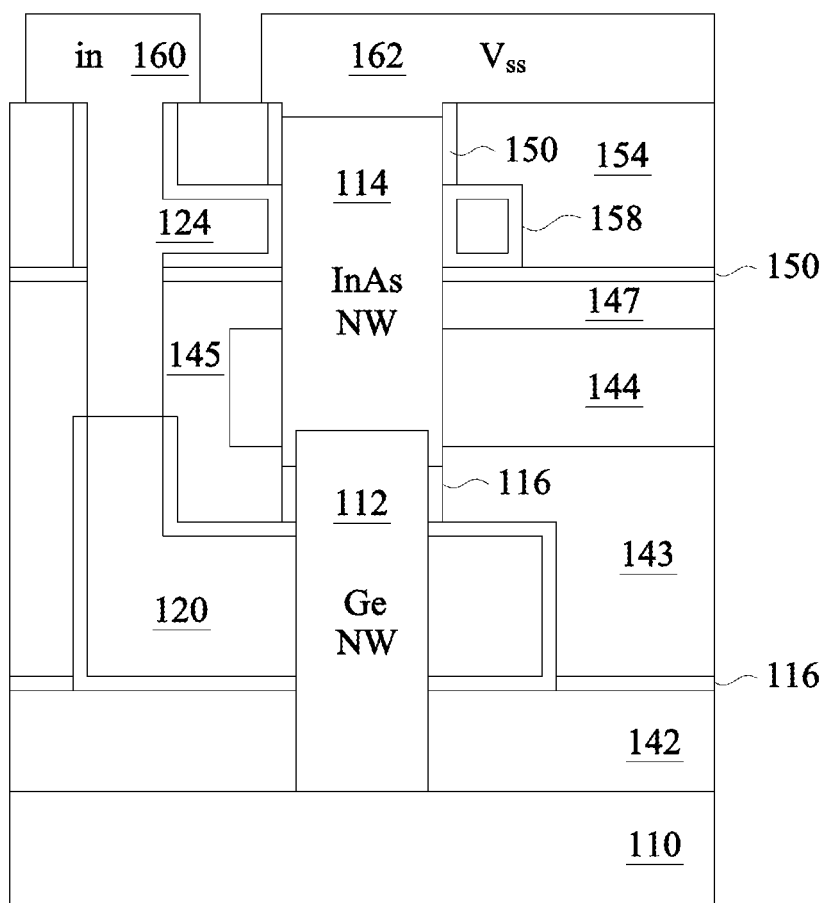


Figure 6W

1

VERTICAL CMOS STRUCTURE AND METHOD

PRIORITY CLAIM AND CROSS-REFERENCE

This application claims priority to U.S. Provisional Application Ser. No. 62/115,986, filed on Feb. 13, 2015 and entitled "Vertical CMOS Structure and Method," which application is hereby incorporated herein by reference.

TECHNICAL FIELD

The present disclosure relates generally to a semiconductor device structures, and, in particular embodiments, to a structure providing vertical complementary transistors and methods for fabricating the structure.

BACKGROUND

The goal of putting more and more devices into integrated circuits has been an important goal in semiconductor manufacturing from the very invention of the integrated circuit. Higher density circuits allow for the manufacture of ever more powerful devices while greatly reducing costs on a per transistor basis. The traditional configuration of circuit elements is to form them laterally on the surface of a semiconductor substrate. This provides ease of manufacturing and reduced complexity. However, currently, semiconductor design engineers are struggling with many limitations to lateral devices.

The greatest challenge is the limits of lithography. The layers of integrated circuits are fabricated by patterning various components using photolithography. In photolithography, a layer of photo-sensitive material called photoresist is coated onto the device. Then the photoresist is exposed a light pattern corresponding to the desired patterns in a particular layer. However, components in integrated circuits have become so small that their size is on the order of the wavelength of light used to expose the photoresist. While various techniques have been employed to push this limitation beyond all reasonable expectation, at some point, this physical limitation will become insurmountable.

To address this challenge, engineers have devised vertically oriented devices. These devices are complex to manufacture. However, they hold the promise of providing compact devices with the functionality of devices that consume much more semiconductor surface area, but without the need to pattern smaller features lithographically. One such vertical device is the vertical gate all-around (VGAA) or nanowire (NW) device.

Of note, prior VGAA or NW techniques provide a transistor of a specific conductivity type. In complementary metal-oxide-semiconductor (CMOS) technology, it is desirable to couple every nMOS transistor to a pMOS transistor. This minimizes off-state leakage in CMOS circuits. To achieve this using prior art VGAA techniques, separate n-channel and p-channel areas must be provided, thus occupying more integrated circuit surface area.

BRIEF DESCRIPTION OF THE DRAWINGS

For a more complete understanding of the present disclosure, and the advantages thereof, reference is now made to the following descriptions taken in conjunction with the accompanying drawings, in which:

2

FIG. 1 is a side view of one embodiment of the present disclosure providing a pair of stacked, complementary transistors;

FIG. 2 is a schematic diagram of the embodiment of FIG. 1;

FIG. 3 is a plan view of the embodiment of FIG. 1;

FIGS. 4A-4V are plan views showing a process, which comprises another embodiment of the present disclosure, for forming the embodiment of FIG. 1;

FIGS. 5A-5E are side view diagrams show alternative processing steps for the process shown in FIGS. 4A-4V, which alternative steps comprise another embodiment of the present disclosure; and

FIGS. 6A-6W are side view diagrams of a process, which comprises another embodiment of the present disclosure, for forming a pair of stacked, complementary transistors, which comprises yet another embodiment of the present disclosure.

DETAILED DESCRIPTION OF ILLUSTRATIVE EMBODIMENTS

The making and using of the present embodiments are discussed in detail below. It should be appreciated, however, that the present disclosure provides many applicable inventive concepts that can be embodied in a wide variety of specific contexts. The specific embodiments discussed are merely illustrative, and do not limit the scope of the disclosure.

The present disclosure will be described with respect to embodiments in a specific context, namely structure using stacked vertical gate-all-around (VGAA) or nanowire (NW) transistors. Even so, the inventive concepts disclosed herein are not limited to the formation of specific structures. Indeed, other structures may also be formed using the inventive concepts disclosed herein. In addition, even though the disclosure is directed toward embodiments VGAA or NW circuits, the inventive concepts disclosed herein may be applied to other types of integrated circuits, electronic structures, and the like.

FIG. 1 shows a side view of one embodiment of the present disclosure. Substrate 10 is a crystalline silicon substrate doped to provide conductivity. Germanium nanowire 12 is formed on the surface of substrate 10 and provides the channel area for p-type transistor 20. Indium Arsenide nanowire 14 is formed on nanowire 12 to provide the channel area for n-type transistor 30. A low reference voltage V_{ss} is provided to the top of nanowire 14 through contact 16. A high reference voltage V_{dd} is provided to substrate 10 through contact 18. It should be noted that a separate V_{dd} contact for each transistor pair is not necessary. A contact such as contact 18 can provide V_{dd} to many transistor pairs.

Gates 22 and 24 provide the gates for transistors 20 and 30, respectively. Gate 22 is separated from nanowire 12 by gate insulator 26. Gate 24 is separated from nanowire 14 by gate insulator 28. In this embodiment, gates 22 and 24 are connected together by contact 32. However, in other configurations, gates 22 and 24 may have separate contacts to allow for differing circuit configurations. Output contact 34 is in contact with nanowire 14 near the junction between nanowire 12 and nanowire 14. This provides an output for the inverter formed by transistors 20 and 30.

FIG. 2 is a schematic representation of the device of FIG. 1, with the components labeled correspondingly. FIG. 3 shows a plan view of the device of FIG. 1.

FIGS. 4A-4V show side views of the process steps for one process for forming the embodiment of FIG. 1. A bottom

3

spacer layer **42** is deposited on substrate **10**. Substrate **10** may be formed of one of many crystalline semiconductive materials, such as crystalline silicon. Substrate **10** is doped to provide conductivity. Spacer layer **42** may be SiO₂ or SiN_x or similar material or combination thereof. Gate contact metal **22** is then deposited on spacer layer **42**. Gate contact metal **22** may be polycrystalline Si, TiN, TaN, W, Al, or similar material or combination thereof. This provides the structure of FIG. 4A. Gate contact metal **22** is then patterned using standard lithographic and etching techniques to provide the structure of FIG. 4B.

Next a dielectric fill layer is added to the exposed portions of spacer layer **42** using chemical vapor deposition or similar techniques. The combined layer **42** is then planarized using conventional chemical-mechanical polishing (CMP) techniques to provide the structure of FIG. 4C. The dielectric fill layer may be SiO₂ or SiN_x or similar material or combination thereof. An additional dielectric fill layer is then added to combined layer **42** to provide the structure of FIG. 4D. This dielectric fill is deposited and planarized using standard deposition and CMP techniques, and may comprise SiO₂ or SiN_x or similar material or combination thereof. The steps for forming this dielectric fill may be deposition then CMP or deposition, followed by CMP, followed by a further deposition.

FIG. 4E shows the next step where drain contact metal **44** is deposited using standard metal deposition techniques. Drain contact metal **44** may be Ti, TiN, TaN, W, Al, or similar material or combination thereof. Drain contact metal **44** is then patterned using standard lithography and etch techniques as shown in FIG. 4F. Combined layer **42** is then expanded as shown in FIG. 4G using standard deposition and CMP techniques to form the bottom spacer for the second level nanowire transistor **30** (FIG. 1). The steps for forming this dielectric fill may be deposition then CMP or deposition, followed by CMP, followed by a further deposition. The dielectric fill layer may be SiO₂ or SiN_x or similar material or combination thereof.

An opening **46** is then etched through dielectric layer **42**, drain contact metal **44** and gate contact metal **22** to substrate **10** as shown in FIG. 4H. Opening **46** may be etched using reactive ion etching or dry etching using SF₆, SiCl₄, C₄F₈, CH₄, H₂, Ar or other known etch gases or combinations thereof. A gate dielectric layer **48** is then deposited using standard conformal deposition techniques as shown in FIG. 4I. Gate dielectric layer **48** can be SiO₂, HfO₂, Al₂O₃, ZrO₂ or similar material or combination thereof. Gate dielectric **48** may comprise a high-K dielectric material. The dielectric thickness can be 1-10 nm. Gate dielectric layer **48** is then etched using an anisotropic etch to result in the configuration shown in FIG. 4J. The anisotropic etch process may be reactive ion etching or dry etching using SF₆, SiCl₄, C₄F₈, CH₄, H₂, Ar or other known etch gases or combination thereof.

The first nanowire **12** is then deposited using a selective epitaxial technique using the silicon substrate as a nucleation site, such as metal-organic chemical vapor deposition (MOCVD) as shown in FIG. 4K. In one embodiment, nanowire **12** comprises crystalline germanium. An additional etching of gate dielectric layer **48** is then performed until the top of gate dielectric layer **48** is approximately 5-15 nanometers below the top of nanowire **12** as shown in FIG. 4L. The etch process may be reactive ion etching or dry etching using SF₆, SiCl₄, C₄F₈, CH₄, H₂, Ar or other known etch gases or combination thereof or wet etch using HF, HCl or similar chemical or combination thereof.

4

The second nanowire channel region **14** is then deposited using a selective epitaxial technique with the first nanowire region **12** serving as a nucleation site, such as MOCVD, as shown in FIG. 4M. In a one embodiment, second nanowire **14** comprises crystalline Indium Arsenide (a group III-V compound semiconductor).

Next an optional dummy gate dielectric **50** is formed using atomic layer deposition (ALD) or CVD as shown in FIG. 4N. Dummy gate dielectric can be SiO₂, SiN, HfO₂, ZrO₂, Al₂O₃ or similar material or combination thereof. The thickness of dummy gate dielectric can be 1-10 nm. Next, gate metal **24** is deposited as shown in FIG. 4O. Gate metal **24** may be poly-Si, TiN, TaN, W, Al, or similar material or combination thereof. Gate metal **24** is then etched back to a thickness as shown in FIG. 4P by etching or a combination of etching with CMP. The etch process may be reactive ion etch using SF₆, SiCl₄, C₄F₈, CH₄, H₂ or other known etch gases or combination thereof or wet etch using HF, HCl, TMAH or similar chemical or combination thereof. Gate metal **24** is then patterned using standard lithographic and etching techniques to the form shown in FIG. 4Q. A dielectric layer **52** is then formed using standard deposition and CMP techniques as shown in FIG. 4R. Dielectric layer **52** may be SiO₂ or SiN_x or similar material or combination thereof.

Next a gate contact hole **54** is formed using standard lithographic and etching techniques as shown in FIG. 4S and extended as shown in FIG. 4T. A two step process is used where a highly controllable etch is used to make the hole of FIG. 4Q and then a more aggressive etch that can etch gate metal layer **22** and **24** is used. The etch processes may be reactive ion etch or dry etch using SF₆, SiCl₄, C₄F₈, CH₄, H₂, Ar or other known etch gases or combination thereof.

A gate metal contact layer **56** is then deposited using standard selective deposition techniques as shown in FIG. 4U. The gate contact layer provides conductive contact to gate layers **22** and **24**. Gate contact layer **56** may be TiN, TaN, W, Al, or similar material or combination thereof. Dummy gate material **50** is removed from the top of upper nanowire channel **14** using standard etch processes. The etch process may be reactive ion etch using SF₆, SiCl₄, C₄F₈, CH₄, H₂ or other known etch gases or combination thereof or wet etch using HF, HCl, TMAH or similar chemical or combination thereof.

Metal contacts **58** are then deposited and patterned using standard deposition and etching techniques to provide contacts to the gate (in), the source of upper transistor **30** (V_{ss}), output contact to **44** (**34**, out FIG. 1), and to the substrate (**18**, V_{dd} FIG. 1) as shown in FIG. 4V. By controlling the doping of germanium nanowire **12** and the relative concentrations of indium and arsenic in nanowire **14**, an inverter is formed with n-channel transistor **30** and p-channel transistor **20**, as shown in FIG. 1. Using different doping and/or relative concentrations, transistor **30** may be p-channel and transistor **20** may be n-channel.

In an alternative embodiment, starting with the structure as shown in FIG. 4S, gate layer **24** and the portion of gate layer **50** between gate layer **24** and nanowire **14** are removed using an etch process. The etch process may be reactive ion etch using SF₆, SiCl₄, C₄F₈, CH₄, H₂ or other known etch gases or combination thereof or wet etch using HF, HCl, TMAH or similar chemical or combination thereof. A replacement gate dielectric **60** is formed using an atomic layer deposition (ALD) technique as shown in FIG. 5A. Gate dielectric **60** can be SiO₂, HfO₂, Al₂O₃, ZrO₂ or

5

similar material or combination thereof and may be a thickness of 1-10 nm. Gate dielectric 60 comprises a high-K dielectric material.

Opening 54 is then extended to gate layer 22 using etching as shown in FIG. 5B. The etching process may be reactive ion etching or dry etching using SF₆, SiCl₄, C₄F₈, CH₄, H₂, Ar or other known etch gases or combination thereof. Opening 54 is then filled using, for example, selective chemical vapor deposition to provide contact 70 and reformed gate layer 24 as shown in FIG. 5C. Then, the portion of dummy gate layer 50 on top of nanowire 14 is removed using etching as shown in FIG. 5D. The etch process may be reactive ion etch using SF₆, SiCl₄, C₄F₈, CH₄, H₂ or other known etch gases or combination thereof or wet etch using HF, HCl, TMAH or similar chemical or combination thereof.

Metal contacts 58 are then deposited and patterned using standard deposition and etching techniques to provide contacts to the gate (in), the source of upper transistor 30 (V_{ss}), output contact to 44 (34, out FIG. 1), and to the substrate (18, V_{dd} FIG. 1) as shown in FIG. 5E. By controlling the doping of germanium nanowire 12 and the relative concentrations of indium and arsenic in nanowire 14, an inverter is formed with n-channel transistor 30 and p-channel transistor 20, as shown in FIG. 1.

Another embodiment of the present disclosure is illustrated in FIGS. 6A-6W. In FIG. 6A, a dielectric layer 142 is formed and patterned on a crystalline silicon substrate 110. Substrate 110 may be Si, GaAs, InP, InAs or similar material or any combination thereof, doped with arbitrary profile n- or p-type (1×10^{16} to 5×10^{20} cm⁻³), or semi-insulating or any combination thereof. Dielectric layer may be SiO₂ or SiNx or similar material or combination thereof.

Nanowire layer 112 is formed using an epitaxial technique, such as MOCVD as shown in FIG. 6B. Nanowire layer 112 may include crystalline germanium. A dummy gate layer 116 is formed on nanowire 112 and dielectric layer 142 followed by sacrificial gate layer 122 as shown in FIG. 6C. Sacrificial gate layer 122 is then etched back as shown in FIG. 6D using etching or a combination of etching and CMP. Sacrificial gate layer may comprise amorphous silicon, poly-silicon, SiO₂, SiN or similar material or combination thereof. The etch process may be reactive ion etch using SF₆, SiCl₄, C₄F₈, CH₄, H₂ or other known etch gases or combination thereof or wet etch using HF, HCl, TMAH or similar chemical or combination thereof. Sacrificial gate layer 122 is then patterned as shown in FIG. 6E using standard photolithographic techniques.

Dielectric layer 143 is then deposited and etched back using standard deposition and CMP techniques to form dielectric layer 143 as shown in FIG. 6F. Dielectric layer 143 may be SiO₂ or SiNx or similar material or combination thereof. Next, an opening 145 is formed using standard lithographic and etch techniques to expose sacrificial gate layer 122 as shown in FIG. 6G. Sacrificial gate 122 and the portion of dummy gate layer 116 adjacent to sacrificial gate 122 are then removed using an etch process to produce opening 118. This etching may be done using techniques such as reactive ion etch using SF₆, SiCl₄, C₄F₈, CH₄, H₂ or other known etch gases or combination thereof or wet etch using HF, HCl, TMAH or similar chemical or combination thereof. The resulting structure is shown in FIG. 6H.

Gate dielectric 117 is then formed on the surfaces of opening 118 using ALD as shown in FIG. 6I. Gate dielectric 117 may comprise SiO₂, HfO₂, Al₂O₃, ZrO₂ or similar material or combination thereof, and has a thickness can be 1-10 nm. Gate 120 is then formed by standard conformal

6

deposition techniques filling opening 118 as shown in FIG. 6J. Gate 120 metal may be TiN, TaN, W, Al, or similar material or combination thereof.

A dielectric layer 145 is then deposited and patterned using standard lithographic techniques as shown in FIG. 6K. The steps to form dielectric layer 145 may include deposition followed by CMP, or may include deposition followed by CMP, which is followed by further deposition. Dielectric layer 145 may comprise SiO₂ or SiNx or similar material or combination thereof. Shared contact layer 144 is deposited and patterned using standard lithographic and etch techniques, which may include CMP techniques, to form shared drain contact 144 as shown in FIG. 6L. Shared drain contact 144 may comprise TiN, TaN, W, Al, or similar material or combination thereof. Dielectric layer 147 is then deposited as shown in FIG. 6M. The steps to form dielectric layer 147 may include deposition followed by CMP, or may include deposition followed by CMP, which is followed by further deposition. Dielectric layer 147 may comprise SiO₂ or SiNx or similar material or combination thereof.

Opening 146 through dielectric layer 147 and shared contact layer 144 is then formed using patterned etching as shown in FIG. 6N. As a part of the process for forming opening 146, dummy gate layer 116 will be removed from the top and partially from the sides of nanowire 112. The etch process may include reactive ion etch or dry etch using SF₆, SiCl₄, C₄F₈, CH₄, H₂, Ar or other known etch gases or combination thereof.

Nanowire 114 is then formed using, for example, MOCVD as shown in FIG. 6O. In a one embodiment, second nanowire 114 comprises Indium-Arsenic in a 3-5 crystalline configuration. Next a dummy gate dielectric 150 is formed using ALD or CVD as shown in FIG. 6P. Dummy gate dielectric 150 can be SiO₂, SiN, HfO₂, ZrO₂, Al₂O₃ or similar material or combination thereof. The thickness of dummy gate dielectric can be 1-10 nm. Next, dummy gate layer 152 is deposited as shown in FIG. 6P. Dummy gate layer 152 may be amorphous silicon, poly-silicon, or similar material. Dummy layer 152 is then etched back to a thickness as shown in FIG. 6Q by etching or a combination of etching with CMP. The etch process may be reactive ion etch using SF₆, SiCl₄, C₄F₈, CH₄, H₂ or other known etch gases or combination thereof or wet etch using HF, HCl, TMAH or similar chemical or combination thereof. Dummy gate layer 152 is then patterned using standard lithographic and etching techniques to provide the structure of FIG. 6R.

Dielectric layer 154 is deposited and planarized using standard deposition and CMP techniques as shown in FIG. 6S. Dielectric layer 154 may be SiO₂ or SiNx or similar material or combination thereof. Next, an opening 156 is formed using standard lithographic and etching techniques as shown in FIG. 6T. Next, dummy gate 152 is removed using SF₆, SiCl₄, C₄F₈, CH₄, H₂ or other known etch gases or combination thereof or wet etch using HF, HCl, TMAH or similar chemical or combination thereof. The portions of dummy gate dielectric 150 thus exposed, are also removed in this process. Gate dielectric 158 is then deposited using ALD technique to provide the structure shown in FIG. 6U. Gate dielectric 158 can be SiO₂, HfO₂, Al₂O₃, ZrO₂ or similar material or combination thereof and may have a thickness of 1-10 nm. Next, opening 156 is extended vertically through gate dielectric 158 and dielectric layers 147 and 145 by etching to expose the top portion of gate 120 as shown in FIG. 6U. The etch process may be reactive ion etch or dry etch using SF₆, SiCl₄, C₄F₈, CH₄, H₂, Ar or other known etch gases or combination thereof.

Next, gate **124** is formed by filling opening **156** and the area vacated when dummy gate **152** was removed using standard selective CVD processes. Gate **124** may comprise TiN, TaN, W, Al, or similar material or combination thereof. The resulting structure is shown in FIG. **6V**. The top portion of dummy gate layer **150** is then removed using standard etching techniques. Then, contacts **160** and **162** are deposited and patterned using standard techniques to provide the resulting structure of FIG. **6W**. Contacts that are not shown will also be provided to shared contact **144** and the substrate **110** (Vdd).

In accordance with one embodiment of the present disclosure, a complementary transistor structure is provided. A lower portion of a column that includes one semiconductive material, such as germanium, is formed on a substrate comprising another semiconductor material, such as silicon. A first gate surrounds and is insulated from the lower portion of the column. An upper portion of the column is provided that includes yet another semiconductive material, such as indium arsenide. A second gate surrounds and is insulated from the lower portion of the column. An electrical contact to the upper portion of the column is provided above the second gate and a second electrical contact is provided to the upper and lower portion of the column between the first and second gates.

In accordance with another embodiment of the present disclosure, a method for forming complementary transistors is provided. A first semiconductor material, forming a lower portion of a column comprising a second semiconductive material, is formed on a semiconductive substrate. The first semiconductive material may be formed using a selective chemical vapor deposition process. A first gate is formed surrounding and insulated from the lower portion of the column. An upper portion of the column is formed including a third semiconductive material. The third semiconductive material may be formed using a selective chemical vapor deposition process using the first semiconductor material as a nucleation site. A second gate is formed surrounding and insulated from the lower portion of the column. Electrical contact to the upper portion of the column above the second gate and electrical contact to the upper and lower portion of the column between the first and second gates are then formed.

An advantage of the embodiments of the present disclosure is providing complementary transistors using a minimum of integrated circuit surface area.

While this invention has been described with reference to illustrative embodiments, this description is not intended to be construed in a limiting sense. Various modifications and combinations of the illustrative embodiments, as well as other embodiments of the invention, will be apparent to persons skilled in the art upon reference to the description. It is therefore intended that the appended claims encompass any such modifications or embodiments.

What is claimed is:

1. A complementary transistor structure comprising:
 - a lower portion of a column comprising a second semiconductive material formed on a substrate comprising a first semiconductor material;
 - a first gate surrounding and insulated from the lower portion of the column;
 - an upper portion of the column comprising a third semiconductive material;
 - a second gate surrounding and insulated from the lower portion of the column;
 - a first electrical contact to the upper portion of the column above the second gate; and

a second electrical contact to the upper portion and lower portion of the column between the first and second gates.

2. The complementary transistor structure as in claim 1 wherein the second semiconductive material is germanium.
3. The complementary transistor structure as in claim 1 wherein the third semiconductive material is indium arsenide.
4. The complementary transistor structure as in claim 1 wherein the second semiconductive material contacts the third semiconductive material.
5. The complementary transistor structure as in claim 1 wherein the second semiconductive material is separated from the third semiconductive material.
6. The complementary transistor structure as in claim 1 wherein the second semiconductive material and the third semiconductive material are opposite conductivity types.
7. The complementary transistor structure as in claim 1 wherein the first gate is electrically coupled to the second gate.
8. The complementary transistor structure as in claim 1 wherein the substrate immediately below the lower portion is electrically coupled to ground.
9. A complementary transistor structure comprising:
 - a lower portion of a column comprising crystalline germanium formed on a silicon substrate;
 - a first gate surrounding and insulated from the lower portion of the column;
 - an upper portion of the column formed on top of the lower portion of the column comprising indium arsenide;
 - a second gate surrounding and insulated from the lower portion of the column;
 - a first electrical contact to the upper portion of the column above the second gate; and
 - a second electrical contact to the upper portion and lower portion of the column between the first and second gates.
10. The complementary transistor structure as in claim 9 wherein the lower portion of the column provides a channel region for a p-type field effect transistor and the upper portion of the column provides a channel region for an n-type field effect transistor.
11. The complementary transistor structure as in claim 9 wherein the lower portion of the column provides a channel region for an n-type field effect transistor and the upper portion of the column provides a channel region for an p-type field effect transistor.
12. The complementary transistor structure as in claim 9 wherein the first gate is insulated from the lower portion of the column by a high-k dielectric.
13. The complementary transistor structure as in claim 9 wherein the second gate is insulated from the upper portion of the column by a high-k dielectric.
14. A complementary transistor structure comprising:
 - a first vertical nanowire extending from a substrate, the first vertical nanowire being a first semiconductor material;
 - a second vertical nanowire extending from the first vertical nanowire, the first vertical nanowire being disposed between the second vertical nanowire and the substrate, the second vertical nanowire being a second semiconductor material different than the first semiconductor material;
 - a first gate adjacent a first channel region of the first vertical nanowire; and

a second gate adjacent a second channel region of the second vertical nanowire, a common source/drain region being interposed between the first gate and the second gate.

15. The complementary transistor structure of claim **14**,
further comprising a gate contact electrically coupled to the first gate and the second gate.

16. The complementary transistor structure of claim **15**,
further comprising an electrical contact electrically coupled to the common source/drain region.

17. The complementary transistor structure of claim **16**,
wherein the first gate and the first vertical nanowire form a first transistor of a first conductivity type, the second gate and the second vertical nanowire form a second transistor of a second conductivity type, the first conductivity type being different than the second conductivity type.

18. The complementary transistor structure of claim **17**,
wherein the first semiconductor material directly contacts the second semiconductor material.

19. The complementary transistor structure of claim **18**,
further comprising a high-k dielectric material interposed between the first gate and the first vertical nanowire and interposed between the second gate and the second vertical nanowire.

20. The complementary transistor structure of claim **16**,
wherein the electrical contact contacts the second vertical nanowire.

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